

เอกสารอ้างอิง



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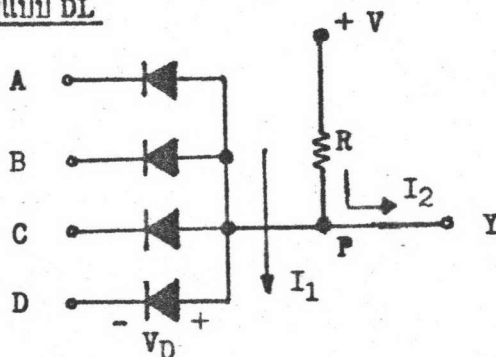
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ภาคผนวก ก.

การคำนวณหาค่าความต้านทานโดยประมาณในวงจรลอจิกเกตแบบ

AND เกตแบบ DL

รูป ก.

วงจรพื้นฐานแสดงดังรูป ก. ในวงจรนี้ค่าความต้านทานสามารถหาได้โดยกำหนดให้

อินพุต D มีสัญญาณลอจิกเป็น "0"

อินพุต A, B, C มีสัญญาณลอจิกเป็น "1"

เพราะฉะนั้นเอาต์พุตจะมีสัญญาณลอจิกเป็น "0" ดังนั้นกระแสจะแยกไหลเป็นสองทางดังรูป และเนื่องจากอินพุตและเอาต์พุตของวงจรนี้คือร่วมกับวงจรไอซีเบอร์ 4040 ดังนั้นกระแส I และ I จะเป็นกระแสซิงค์ (sink current) ที่ไหลเข้าไปยังไอซี

จากคู่มือการใช้งานของ 4040 กำหนดว่า

$$\text{เมื่อ } V_{DD} = 5 \text{ โวลต์}$$

$$V_{OL} = 0.4 \text{ โวลต์}$$

$$I_{OL} = 0.5 \text{ มิลลิแอมป์}$$

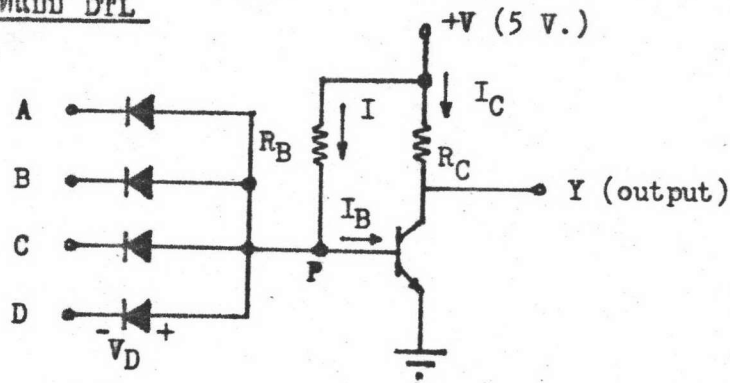
$$\text{แรงดันที่จุด P} = V_D + V_{OL}$$

$$= 0.65 + 0.4$$

$$= 1.05 \text{ โวลต์}$$

เพราะฉะนั้นความต้านทานต่ำสุด (R_{min}) = $(V - V_P)/I$
 = $(5 - 1.05)/I$
 = $3.95/0.5$ (กำหนด $I = 0.5 \text{ mA}$)
 = 7.9 กิโลโห์ม

NAND เกทแบบ DTL



ค่า R_B และ R_C หาได้โดยกำหนดให้

อินพุต A, B, C มีลอจิกเป็น "1"

อินพุต D มีลอจิกเป็น "0"

เพราะฉะนั้นเอาต์พุตจะมีลอจิกเป็น "1" นั่นคือทรานซิสเตอร์ OFF ($I_C = I_B = 0$)

ดังนั้นกระแส I จะไหลผ่านไดโอดของอินพุต D ในกรณีนี้จะกำหนดให้ I_{OL} มีค่าต่ำกว่าในคู่มือการใช้งานเพื่อให้ค่า V_{OL} มีค่าเกือบเป็นศูนย์ เพราะฉะนั้น $V_P = V_D = 0.65$ โวลต์ ($V_{OL} = 0$)

กำหนดให้ $I_{OL} = 0.1$ มิลลิแอมป์

เพราะฉะนั้น $R_B(\text{min.}) = (V - V_P)/I_{OL}$
 = $(5 - 0.65)/0.1$
 = 43.5 กิโลโห์ม

เลือกใช้ $R_B = 47$ กิโลโห์ม

ค่าต้านทาน R_C หาได้โดยเมื่อทรานซิสเตอร์ ON กระแส I_C (กระแส I_C เท่ากับกระแสที่ไหลมายังเอาต์พุตรวมกับกระแสไหลผ่านทรานซิสเตอร์) ควรมีค่าไม่เกิน

$$\text{หนึ่งมิลลิแอมป์} \quad \text{ดังนั้น } R_C = (V - V_{CE(\text{Sat.})})/I_C$$

$$R_C(\text{min}) = (5 - 0.2)/1 \text{ mA}$$

$$= 4.8 \text{ กิโลโห์ม}$$

$$\text{เลือกใช้} = 5.6 \text{ กิโลโห์ม}$$

เมื่อหาค่าความต้านทานทั้งสองได้แล้วจำเป็นต้องตรวจสอบว่า วงจรนี้สามารถทำงานได้จริง วิธีตรวจสอบทำได้โดยการสมมติเมื่อทรานซิสเตอร์อยู่ในสถานะ ON ดังนั้น กระแส I_C จะเท่ากับ

$$I_C = (5 - 0.2)/5.6k$$

$$= 0.857 \text{ มิลลิแอมป์}$$

$$I_B = I_C/H_{FE(\text{min})} \quad ; \quad H_{FE} = 110$$

$$= 0.008 \text{ มิลลิแอมป์}$$

$$\text{แต่ในวงจรที่ใช้ } I_B \text{ มีค่า} = (5 - 0.8)/47k$$

$$= 0.089 \text{ มิลลิแอมป์}$$

เพราะฉะนั้นจะเห็นว่าค่าของกระแส I_B ภายในวงจรมีค่ามากเกินไปกว่าค่าที่กำหนดไว้ สรุปได้ว่าทรานซิสเตอร์อยู่ในสถานะ ON จริงและวงจรนี้สามารถทำงานได้จริง.

ภาคผนวก ข.

คู่มือการใช้งานของวงจรไอซีเบอร์ต่างๆที่ใช้ในการออกแบบ

SCL4001UB

CMOS NOR GATE (Unbuffered)

FEATURES

- ◆ Unbuffered Outputs for Quasi-Linear Applications
- ◆ Quad 2-Input NOR Configuration
- ◆ Diode Protection on all Inputs
- ◆ Output Drive Current Compatible with "B" Series
- ◆ Pin Compatible with Buffered SCL4001B
- ◆ Balanced Output Drive Current Specifications

DESCRIPTION

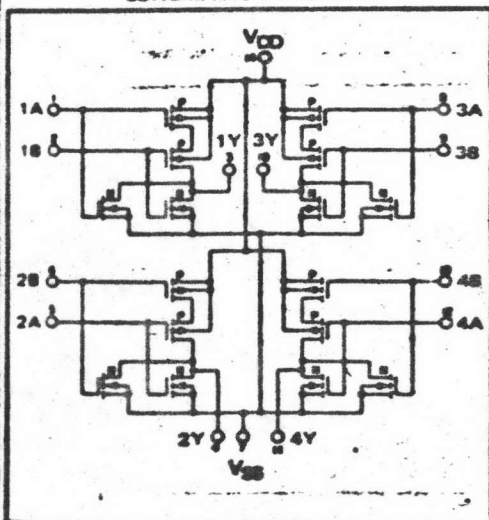
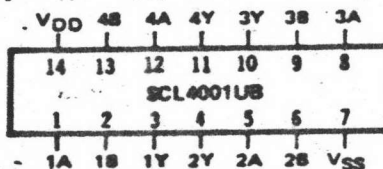
The SCL4001UB consists of four positive-logic NOR gates. The outputs are unbuffered, making the device suitable for quasi-linear applications, such as gated oscillators, multivibrators, and pulse shaping circuits.

For digital applications, the buffered SCL4001B is recommended for its higher gain and input pattern insensitivity.

TRUTH TABLE

Inputs	Output
0 0	1
All other combinations	0

SCHEMATIC DIAGRAM

CONNECTION DIAGRAM
(all packages)

Add suffix for package:

- C 14-pin CerDip
- D 14-pin Ceramic
- E 14-pin Epoxy
- F 14-pin Flat
- H Chip

RECOMMENDED OPERATING CONDITIONS

For maximum reliability:

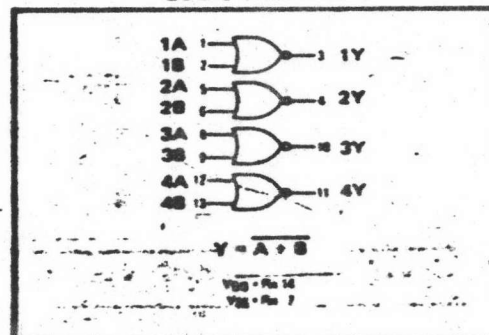
DC Supply Voltage $V_{DD} - V_{SS}$ 3 to 15 Vdc

Operating Temperature T_A

C, D, F, H Device -55 to +125 °C

E Device -40 to +85 °C

LOGIC DIAGRAM



ELECTRICAL CHARACTERISTICS

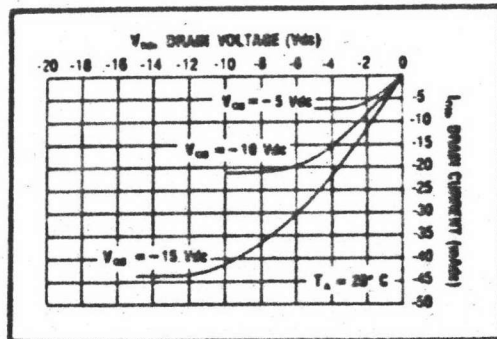
STATIC CHARACTERISTICS

PARAMETER	V _{DD} (Vdc)	CONDITIONS	T _{LOW} ²		+25°C			T _{HIGH} ³		Units
			Min.	Max.	Min.	Typ.	Max.	Min.	Max.	
QUIESCENT DEVICE CURRENT	I _{DD}	V _{IN} = V _{SS} or V _{DD} All valid input combinations	5	0.05	0.0005	0.05	1.5	μA _{DC}		
			10	0.10	0.001	0.10	3.0			
			15	0.20	0.002	0.20	6.0			

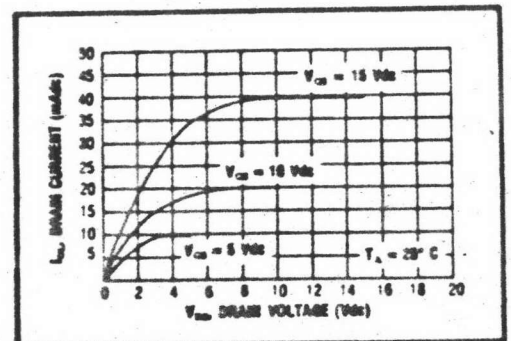
- NOTES: ¹ Remaining Static Electrical Characteristics are listed under "SCL4000B Series Family Specifications".
² T_{LOW} = -55°C for C, D, F, H device.
 = -40°C for E device.
 T_{HIGH} = +125°C for C, D, F, H device.
 = + 85°C for E device.
³ This device has been designed for balanced output drive current specifications. Consult Family Specifications.

DYNAMIC CHARACTERISTICS (C_L = 50pF, T_A = 25°C)

PARAMETER	V _{DD} (Vdc)	Min.	Typ.	Max.	Units
PROPAGATION DELAY TIME	t _{PLH} , t _{PHL}	5	75	150	ns
		10	35	70	
		15	25	50	
OUTPUT TRANSITION TIME	t _{PLH} , t _{PHL}	5	100	200	ns
		10	50	100	
		15	40	80	



Typical P-Channel Source Current Characteristics



Typical N-Channel Sink Current Characteristics

SCL4009UB Inverting
SCL4010B Non-Inverting

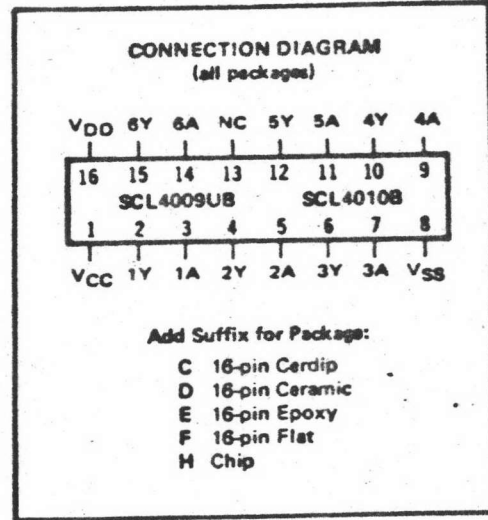
CMOS
HEX BUFFERS/CONVERTERS

FEATURES

- ◆ Direct Drive of 2 TTL/DTL Loads
- ◆ Operation from Single or Dual Supplies
- ◆ All Inputs Diode-Protected

DESCRIPTION

The SCL4009UB and SCL4010B are single-chip monolithic silicon integrated circuits containing eighteen N-Channel and twelve P-Channel enhancement-mode MOS transistors connected to form six independent buffer/convertor configurations. These devices are designed for use as hex CMOS-to-DTL or TTL logic level converters or hex CMOS current drivers. Conversion ranges are from CMOS logic operating at 3Vdc to 18Vdc supply levels to DTL or TTL logic operating at 3Vdc to 6Vdc supply levels. Conversion to logic output levels greater than 6Vdc is permitted providing $V_{CC} < V_{DD}$.



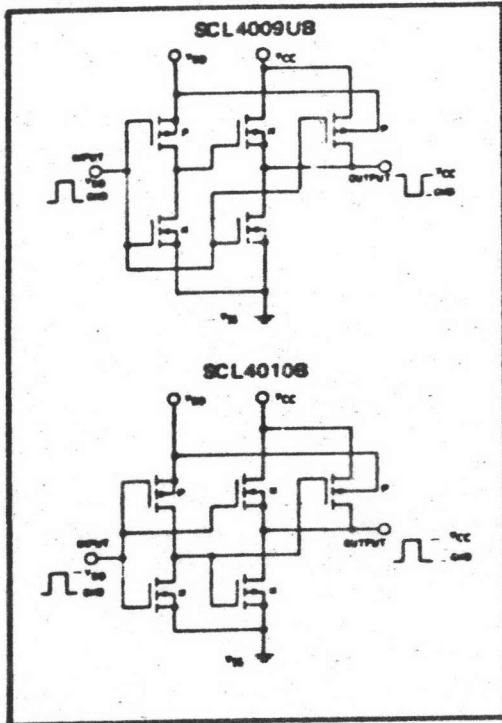
RECOMMENDED OPERATING CONDITIONS

For maximum reliability:

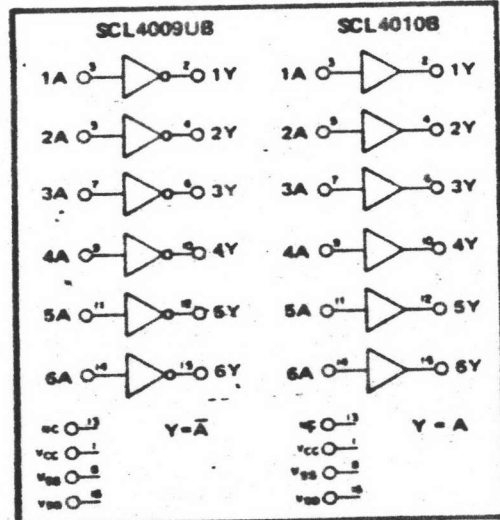
DC Supply Voltage $V_{DD} - V_{SS}$ 3 to 15 Vdc
 $V_{CC} - V_{SS}$ 3 to 15 Vdc
 $V_{CC} < V_{DD}$

Operating Temperature T_A -55 to +125 °C
 C, D, F, H Device
 E Device -40 to +85 °C

SCHEMATIC DIAGRAMS



LOGIC DIAGRAMS



ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS^{1, 2}

PARAMETER	V _{DD} (V _{Dc})	CONDITIONS	T _{LOW} ³		+25°C			T _{HIGH} ³		Units		
			Min.	Max.	Min.	Typ.	Max.	Min.	Max.			
QUIESCENT DEVICE CURRENT	I _{DD}	V _{IN} = V _{SS} or V _{DD} All valid input combinations	5	1.0	-	0.005	1.0	-	30	μAdc		
			10	2.0	-	0.01	2.0	-	60			
			15	4.0	-	0.02	4.0	-	120			
MINIMUM INPUT HIGH VOLTAGE SCL4009UB	V _{IN}	V _{OL} = 0.5V V _{OL} = 1.0V V _{OL} = 1.5V I _O < 1μA	5	4.0	-	2.75	4.0	-	4.0	Vdc		
			10	8.0	-	5.5	8.0	-	8.0			
			15	12.0	-	8.25	12.0	-	12.0			
MAXIMUM INPUT LOW VOLTAGE SCL4009UB	V _{IL}	V _{OH} = 3.6V V _{OH} = 7.2V V _{OH} = 10.8V I _O < 1μA	5	1.0	-	1.0	2.25	-	1.0	Vdc		
			10	2.0	-	2.0	4.5	-	2.0			
			15	3.0	-	3.0	6.75	-	3.0			
OUTPUT LOW (SINK) CURRENT C, D, F, H device	I _{OL}	V _{OL} = 0.4V V _{OL} = 0.5V V _{OL} = 1.5V V _{IN} = V _{SS} or V _{DD}	5	3.8	-	3.0	4.0	-	2.2	mAdc		
			10	10.0	-	8.0	10	-	5.6			
			15	30	-	24	36	-	16			
			E device	V _{OL} = 0.4V V _{OL} = 0.5V V _{OL} = 1.5V V _{IN} = V _{SS} or V _{DD}	5	3.6	-	3.0	4.0	-	2.4	mAdc
					10	9.6	-	8.0	10	-	6.4	
					15	28	-	24	36	-	20	

NOTES: ¹ Remaining Static Electrical Characteristics are listed under "SCL4000B Series Family Specifications".

² T_{LOW} = -55°C for C, D, F, H device
= -40°C for E device.

T_{HIGH} = +125°C for C, D, F, H device
= +85°C for E device.

³ V_{CC} = V_{DD}

DYNAMIC CHARACTERISTICS (C_L = 50pF, T_A = 25°C)

PARAMETER	V _{DD} (V _{Dc})	V _{CC} (V _{Dc})	Min.	Typ.	Max.	Units		
PROPAGATION DELAY TIME Driving CMOS	I _{PLH}	5 10 15	5	60	120	ns		
			10	35	70			
			15	28	56			
			Driving TTL/DTL	5 10 15	5	45	90	ns
					10	20	40	
					15	15	30	
Driving CMOS	I _{PHL}	5 10 15	5	30	60	ns		
			10	18	36			
			15	12	24			
			Driving TTL/DTL	5 10 15	5	35	70	ns
					10	15	30	
					15	10	20	
OUTPUT TRANSITION TIME	I _{TLH}	5 10 15	5	150	300	ns		
			10	75	150			
			15	60	120			
			I _{TNL}	5 10 15	5	30	60	ns
					10	20	40	
					15	12	24	
INPUT CAPACITANCE SCL4009UB SCL4010B	C _{IN}	-	-	10	15	pF		
		-	-	5	7.5			



SCL4011UB

CMOS NAND GATE (Unbuffered)

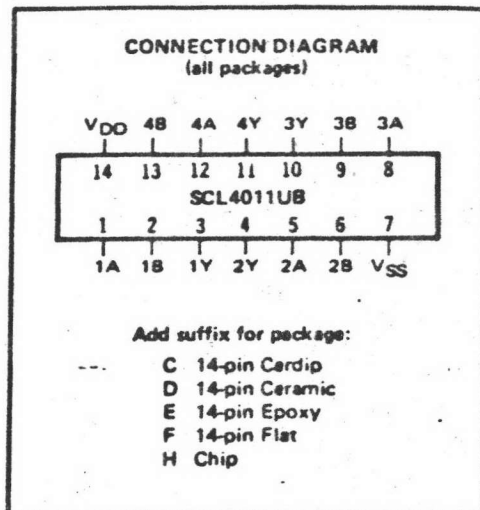
FEATURES

- ◆ Unbuffered Outputs for Quasi-Linear Applications
- ◆ Quad 2-Input NAND Configuration
- ◆ Diode Protection on all Inputs
- ◆ Output Drive Current Compatible with "B" Series
- ◆ Pin Compatible with Buffered SCL4011B
- ◆ Balanced Output Drive Current Specifications

DESCRIPTION

The SCL4011UB consists of four positive-logic NAND gates. The outputs are unbuffered, making the device suitable for quasi-linear applications, such as gated oscillators, multivibrators, and pulse shaping circuits.

For digital applications, the buffered SCL4011B is recommended for its higher gain and input pattern insensitivity.



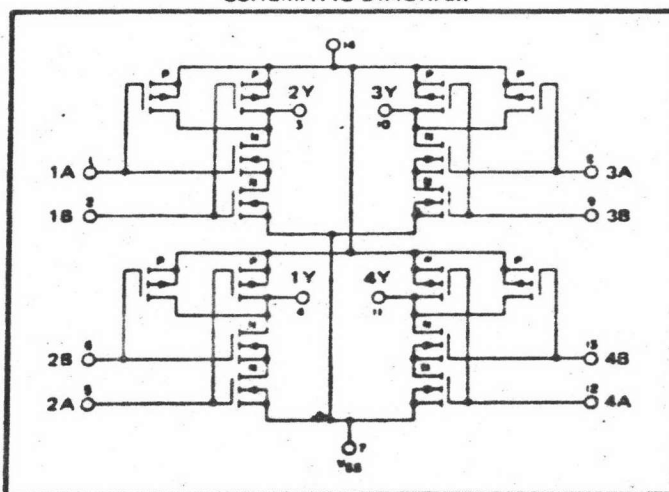
TRUTH TABLE

Inputs		Output
1	1	0
All other combinations		1

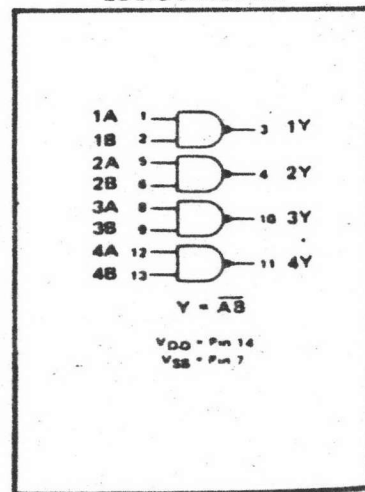
RECOMMENDED OPERATING CONDITIONS

For maximum reliability:
 DC Supply Voltage V_{DD} - V_{SS} 3 to 15 V_{DC}
 Operating Temperature T_A
 C, D, F, H Device -55 to +125 °C
 E Device -40 to +85 °C

SCHEMATIC DIAGRAM



LOGIC DIAGRAM



ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS ^{1,2}

PARAMETER	V _{DD} (Vdc)	CONDITIONS	T _{LOW} ³		+25°C			T _{HIGH} ³		Units
			Min.	Max.	Min.	Typ.	Max.	Min.	Max.	
QUIESCENT DEVICE CURRENT	I _{DD}	V _{IN} = V _{SS} or V _{DD} All valid input combinations	-	0.05	-	0.0005	0.05	-	1.5	μAde
			-	0.10	-	0.001	0.10	-	3.0	
			-	0.20	-	0.002	0.20	-	6.0	

NOTES: ¹ Remaining Static Electrical Characteristics are listed under "SCL4000B Series Family Specifications".

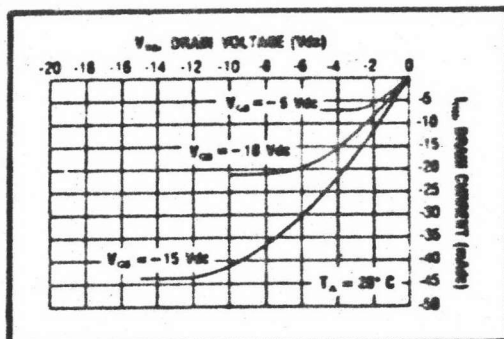
² T_{LOW} = -55°C for C, D, F, H device.
= -40°C for E device.

T_{HIGH} = +125°C for C, D, F, H device.
= + 85°C for E device.

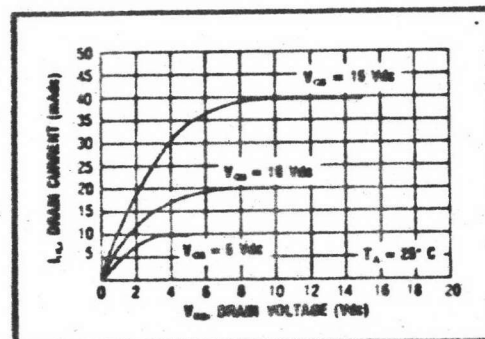
³ This device has been designed for balanced output drive current specifications. Consult Family Specifications.

DYNAMIC CHARACTERISTICS (C_L = 50pF, T_A = 25°C)

PARAMETER		V _{DD} (Vdc)	Min.	Typ.	Max.	Units
PROPAGATION DELAY TIME	t _{PLH} , t _{PHL}	5	-	75	150	ns
		10	-	35	70	
		15	-	25	50	
OUTPUT TRANSITION TIME	t _{TLH} , t _{TML}	5	-	100	200	ns
		10	-	50	100	
		15	-	40	80	



Typical P-Channel
Source Current Characteristics



Typical N-Channel
Sink Current Characteristics

SCL4016AB

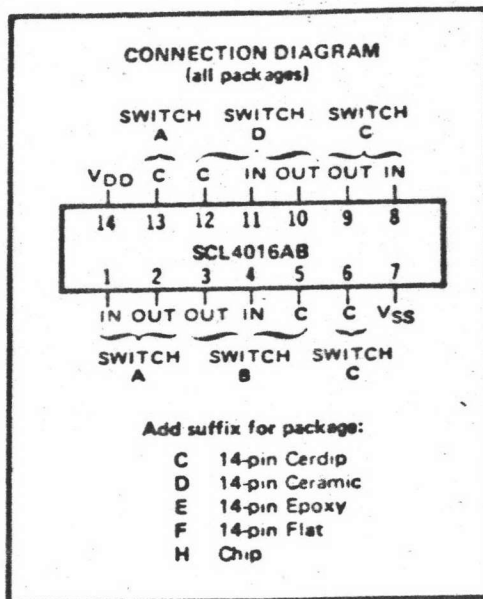
CMOS QUAD ANALOG SWITCH

FEATURES

- ◆ Wide Range of Digital and Analog Signal Levels - Digital or Analog Signals to 18 Volts peak
- ◆ Low ON Resistance - 200 Ω typ. over 15Vp-p Signal Input Range, @ 15Vdc
- ◆ Matched Switch Characteristics - 10 Ω typ. Difference between RON Values at a Fixed Bias Point over 15Vp-p Signal Input Range @ 15Vdc
- ◆ High On/Off Output Voltage Ratio - 65 dB typ. @ $f_{is} = 10\text{kHz}$, $R_L = 10\text{k}\Omega$
- ◆ High degree of Linearity - $< 0.4\%$ Distortion typ. @ $f_{is} = 1\text{kHz}$, $V_{is} = 5\text{V}_{p-p}$, $V_{DD} - V_{SS} > 10\text{V}$, $R_L = 10\text{k}\Omega$
- ◆ Extremely Low OFF Switch Leakage Resulting in Very Low Offset Current and High Effective OFF resistance - 10pA typ. @ $V_{DD} - V_{SS} = 10\text{V}$, $T_A = 25^\circ\text{C}$
- ◆ Extremely High Control Input Impedance (Control Circuit Isolated from Signal Circuit) - $10^{12}\Omega$ typ.
- ◆ Low Crosstalk between Switches - -50dB typ. @ $f_{is} = 0.9\text{MHz}$, $R_L = 1\text{k}\Omega$
- ◆ Matched Control-Input to Signal-Output Capacitances - Reduces Output Signal Transients
- ◆ Transmits Frequencies up to 40MHz

DESCRIPTION

The SCL4016AB is a single-chip monolithic silicon integrated circuit containing eight N-channel and eight P-channel enhancement-mode MOS transistors connected to form four independent bilateral signal switches. Each switch consists of both P- and N-channel devices with common source and drain connections. A single control signal is required per switch. Both P and N devices in a given switch are biased ON or OFF by the control signal. The CMOS switch permits peak input-signal voltage swings equal to the full supply voltage, a considerable advantage over single-channel types.

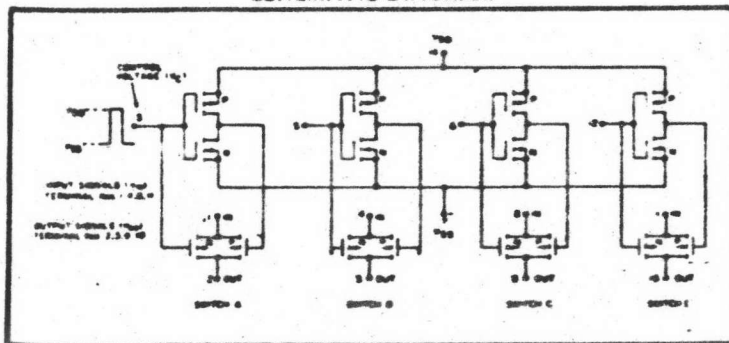


RECOMMENDED OPERATING CONDITIONS

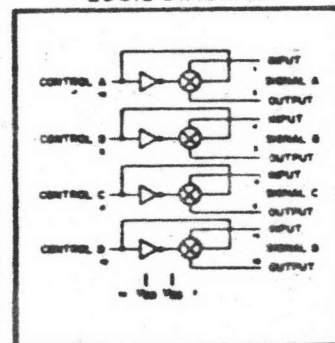
For maximum reliability:

DC Supply Voltage	$V_{DD} - V_{SS}$	3 to 15	Vdc
Operating Temperature	T_A	-55 to +125	$^\circ\text{C}$
C, D, F, H Device		-40 to +85	$^\circ\text{C}$
E Device			

SCHEMATIC DIAGRAM



LOGIC DIAGRAM



ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS¹

PARAMETER	CONDITIONS	V _{SS} (Vdc)	V _{DD} (Vdc)	T _{LOW} ²			25°C			T _{HIGH} ²		Units	
				Min.	Max.	Min.	Typ.	Max.	Min.	Max.			
QUIESCENT DEVICE CURRENT I _{DD}	V _{IN} = V _{SS} or V _{DD} All valid input combinations	0	5	-	0.05	-	0.0005	0.05	-	15	μAde		
		0	10	-	0.1	-	0.001	0.1	-	30			
		0	15	-	0.2	-	0.002	0.2	-	60			
MINIMUM INPUT HIGH VOLTAGE (Control Input) V _{IH}	V _{IS} = V _{SS} V _{OS} = V _{DD} I _{OS} = 10μA	0	5	-	2.9	-	1.5	2.9	-	2.4	Vdc		
		0	10	-	2.9	-	1.5	2.7	-	2.4			
		0	15	-	2.9	-	1.5	2.7	-	2.4			
MAXIMUM INPUT LOW VOLTAGE (Control Input) V _{IL}	V _{IS} = V _{SS} V _{OS} = V _{DD} I _{OS} = 10μA	0	5	0.9	-	0.7	1.5	-	0.4	-	Vdc		
		0	10	0.9	-	0.7	1.5	-	0.4	-			
		0	15	0.9	-	0.7	1.5	-	0.4	-			
SWITCH INPUT/OUTPUT LEAKAGE (Switch off) I _{OFF}	V _C = V _{SS} V _{IS}	±7.5	+7.5	-	±250	-	±0.1	±250	-	±2500	nAde		
		±5	+5	-	±125	-	±0.01	±125	-	±1250			
ON RESISTANCE C, D, F, H device E device	R _{ON} V _C = V _{DD} R _L = 10kΩ	V _{IS} (Vdc)	7.5	+7.5	-	390	-	200	400	-	600	Ω	
					+7.5	-	390	-	200	400	-		600
					-7.5	-	775	-	290	850	-		1230
		±0.25	+5	-	800	-	250	660	-	960	Ω		
			-5	-	600	-	250	660	-	960			
			±0.25	-	1870	-	580	2000	-	2600			
	R _{ON} V _C = V _{DD} R _L = 10kΩ	V _{IS} (Vdc)	7.5	+7.5	-	370	-	200	400	-	520	Ω	
					+7.5	-	370	-	200	400	-		520
					-7.5	-	790	-	280	850	-		1080
		±0.25	+5	-	610	-	250	660	-	840	Ω		
			-5	-	610	-	250	660	-	840			
			±0.25	-	1900	-	580	2000	-	2380			
R _{ON} V _C = V _{DD} R _L = 10kΩ	V _{IS} (Vdc)	7.5	+7.5	-	370	-	200	400	-	520	Ω		
				+7.5	-	370	-	200	400	-		520	
				-7.5	-	790	-	300	850	-		1080	
	±0.25	+10	-	610	-	250	660	-	840	Ω			
		+0.25	-	610	-	250	660	-	840				
		-0.25	-	1900	-	580	2000	-	2380				
ON RESISTANCE MATCH (Same package) ΔR _{ON}	V _C = V _{DD} R _L = 10kΩ	V _{IS} (Vdc)	7.5	+7.5	-	-	-	10	-	-	Ω		
					±5	-	-	-	15	-		-	

- NOTES: ¹ Remaining Static Electrical Characteristics are listed under "SCL4000B Series Family Specifications".
² T_{LOW} = -55°C for C, D, F, H device.
 = -40°C for E device.
 T_{HIGH} = +125°C for C, D, F, H device.
 = +85°C for E device.
³ This device has been designed for balanced output drive current specifications. Consult Family Specifications.

DYNAMIC CHARACTERISTICS (C_L = 50 pF, T_A = 25°C)

PARAMETER	CONDITIONS	V _{SS} (Vdc)	V _{DD} (Vdc)	Min.	Typ.	Max.	UNIT
SIGNAL INPUTS (V _{IS}) AND OUTPUTS (V _{OS})							
PROPAGATION DELAY TIME Signal input to signal output	t _{PLH} , t _{PHL} V _C = V _{DD} V _{IS} = square wave R _L = 10kΩ	0	5	-	.20	40	ns
		0	10	-	.10	20	
		0	15	-	.75	15	
BANDWIDTH (-3dB) (Sine Wave) BW	V _C = V _{DD} V _{IS} = 5V _{DD} carried @ 0Vdc	R _L		5	+5	-	MHz
		1kΩ				54	
		10kΩ				40	
		100kΩ				38	
		1MΩ		37			

SCL4022AB

CMOS OCTAL COUNTER/DIVIDER

FEATURES

- ◆ Eight Decoded Outputs
- ◆ Direct Reset
- ◆ Trigger from either Edge of Clock Input
- ◆ Carry Output for Cascading Stages
- ◆ Fully Static Operation - DC to 5MHz @ 10Vdc

DESCRIPTION

The SCL4022AB consists of a 4-stage Johnson Divide-by-8 Counter and an Output Decoder. Inputs include Clock, Reset, and Clock Enable signals.

The counter has interchangeable Clock and Clock Enable lines for incrementing on either a positive-going or negative-going transition, respectively. A high Reset signal clears the counter to its zero count.

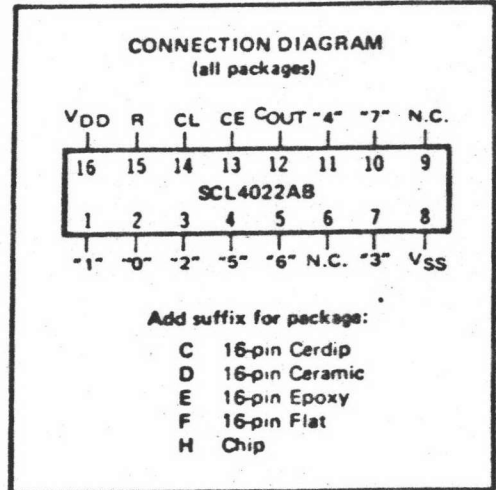
Use of the Johnson divide-by-eight counter configuration permits high-speed operation, 2-input decode gating, and spike-free decoded outputs. Anti-lock gating is provided, thus assuring proper counting sequence. The 8 decoded outputs are normally low and go high only at their respective decoded time slot. Each decoded output remains high for one full clock cycle. A Carry-out (COUT) signal completes one cycle every 8 clock input cycles and is used to directly clock the succeeding counter in multi-stage applications.

This part can be used in frequency division circuits as well as octal counter or octal decode display applications.

FUNCTIONAL TRUTH TABLE
(Positive Logic)

Clock	Clock Enable	Reset	Output = n
0	X	0	n
X	1	0	n
↕	0	0	n + 1
	X	0	n
1	↕	0	n + 1
X		0	n
X	X	1	"0"

X Don't Care If n < 4 Carry = 1, otherwise = 0

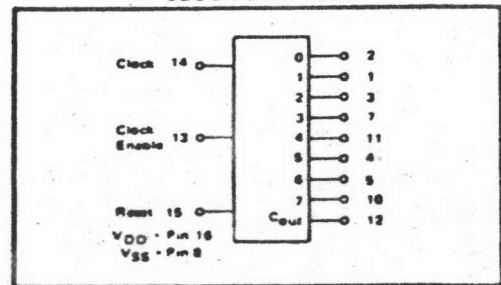


RECOMMENDED OPERATING CONDITIONS

For maximum reliability:

DC Supply Voltage	VDD - VSS	3 to 15	Vdc
Operating Temperature	TA	-55 to +125	°C
C, D, F, H Device		-40 to +85	°C
E Device			

BLOCK DIAGRAM



ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS¹

PARAMETER	V _{DD} (Vdc)	CONDITIONS	T _{LOW} ²		+25°C			T _{HIGH} ²		Units	
			Min.	Max.	Min.	Typ.	Max.	Min.	Max.		
QUIESCENT DEVICE CURRENT	I _{DD}	5	V _{IN} = V _{SS} or V _{DD} All valid input combinations	-	5	-	0.05	6	-	150	μAdc
		10		-	10	-	0.1	10	-	300	
		15		-	20	-	0.2	20	-	600	
OUTPUT HIGH (SOURCE) CURRENT C, D, F, H device: Decoded Outputs Carry Output E device: Decoded Outputs Carry Output	I _{OH}	5	V _{OH} = 4.6V	-0.05	-	-0.04	-0.3	-	-0.028	-	mAdc
		10	V _{OH} = 9.5V	-0.125	-	-0.1	-0.75	-	-0.07	-	
		15	V _{OH} = 13.5V V _{IN} = V _{SS} or V _{DD}	-0.375	-	-0.3	-2.5	-	-0.21	-	
		5	V _{OH} = 4.6V	-0.25	-	-0.2	-0.75	-	-0.14	-	mAdc
		10	V _{OH} = 9.5V	-0.62	-	-0.5	-1.1	-	-0.35	-	
		15	V _{OH} = 13.5V V _{IN} = V _{SS} or V _{DD}	-1.9	-	-1.5	-3.5	-	-1.1	-	
		5	V _{OH} = 4.6V	-0.048	-	-0.04	-0.3	-	-0.032	-	mAdc
		10	V _{OH} = 9.5V	-0.12	-	-0.1	-0.75	-	-0.08	-	
		15	V _{OH} = 13.5V V _{IN} = V _{SS} or V _{DD}	-0.36	-	-0.3	-2.5	-	-0.24	-	
		5	V _{OH} = 4.6V	-0.24	-	-0.2	-0.75	-	-0.16	-	mAdc
		10	V _{OH} = 9.5V	-0.6	-	-0.5	-1.1	-	-0.4	-	
		15	V _{OH} = 13.5V V _{IN} = V _{SS} or V _{DD}	-1.8	-	-1.5	-3.5	-	-1.2	-	
OUTPUT LOW (SINK) CURRENT C, D, F, H device: Decoded Outputs Carry Output E device: Decoded Outputs Carry Output	I _{OL}	5	V _{OL} = 0.4V	0.05	-	0.04	0.4	-	0.028	-	mAdc
		10	V _{OL} = 0.5V	0.125	-	0.1	1.0	-	0.07	-	
		15	V _{OL} = 1.5V V _{IN} = V _{SS} or V _{DD}	0.375	-	0.3	3.0	-	0.21	-	
		5	V _{OL} = 0.4V	0.25	-	0.2	0.75	-	0.14	-	mAdc
		10	V _{OL} = 0.5V	0.62	-	0.5	1.3	-	0.35	-	
		15	V _{OL} = 1.5V V _{IN} = V _{SS} or V _{DD}	1.9	-	1.5	4.0	-	1.1	-	
		5	V _{OL} = 0.4V	0.048	-	0.04	0.4	-	0.032	-	mAdc
		10	V _{OL} = 0.5V	0.12	-	0.1	1.0	-	0.08	-	
		15	V _{OL} = 1.5V V _{IN} = V _{SS} or V _{DD}	0.36	-	0.3	3.0	-	0.24	-	
		5	V _{OL} = 0.4V	0.24	-	0.2	0.75	-	0.16	-	mAdc
		10	V _{OL} = 0.5V	0.6	-	0.5	1.3	-	0.4	-	
		15	V _{OL} = 1.5V V _{IN} = V _{SS} or V _{DD}	1.8	-	1.5	4.0	-	1.2	-	

NOTES: ¹ Remaining Static Electrical Characteristics are listed under "SCL4000B Series Family Specifications".

² T_{LOW} = -55°C for C, D, F, H device.
= -40°C for E device.

T_{HIGH} = +125°C for C, D, F, H device.
= +85°C for E device.

SCL4024B

CMOS 7-STAGE BINARY COUNTER

FEATURES

- ◆ 7 Fully Static Stages
- ◆ Buffered Outputs Available from All Stages
- ◆ Common Reset Line
- ◆ 8 MHz Counting Rate @ 10Vdc
- ◆ All Inputs Buffered

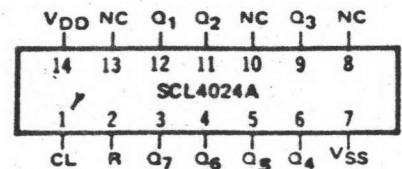
DESCRIPTION

The SCL4024B is a single chip monolithic medium scale integrated circuit containing N-Channel and P-Channel enhancement-mode MOS transistors. Seven single-phase clocked counting stages are provided with the Q output of each stage accessible. The Counter is reset to "zero" by a high level on the Reset input. Each counter stage is a static master-slave flip-flop. The counter state is advanced one count on the negative-going transition of each input pulse.

TRUTH TABLE

Clock	Reset	State
0	0	No Change
0	1	All Outputs Low
1	0	No Change
1	1	All Outputs Low
	0	No Change
	1	All Outputs Low
	0	Advance One Count
	1	All Outputs Low

CONNECTION DIAGRAM (all packages)



Add suffix for package:

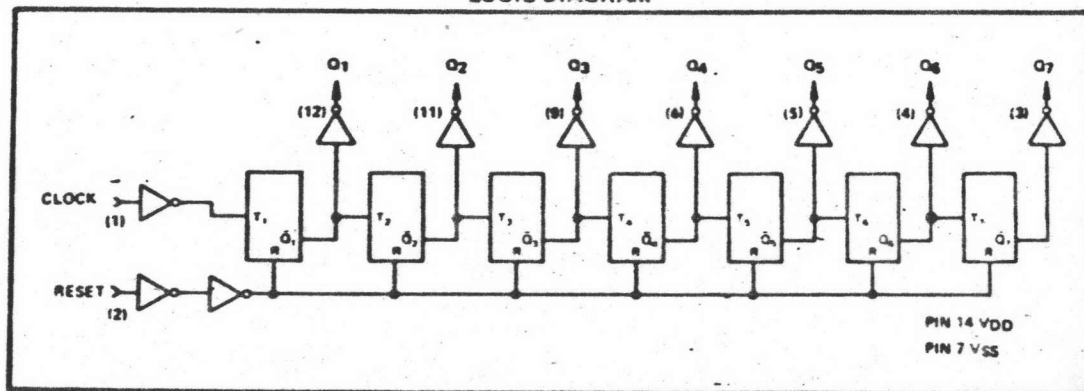
- C 14-pin Cerdip
- D 14-pin Ceramic
- E 14-pin Epoxy
- F 14-pin Flat
- H Chip

RECOMMENDED OPERATING CONDITIONS

For maximum reliability:

DC Supply Voltage	VDD - VSS	3 to 15	Vdc
Operating Temperature	TA	-55 to +125	°C
C, D, F, H Device		-40 to +85	°C
E Device			

LOGIC DIAGRAM



ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS¹

PARAMETER	V _{DD} (V _{Ddc})	CONDITIONS	T _{LOW} ²		+25°C			T _{HIGH} ³		Units
			Min.	Max.	Min.	Typ.	Max.	Min.	Max.	
QUIESCENT DEVICE CURRENT	I _{DD}	V _{IN} = V _{ES} or V _{DD} All valid input combinations	-	5	-	0.05	5	-	150	μA _{dc}
			-	10	-	0.1	10	-	300	
			-	20	-	0.2	20	-	600	

NOTES: ¹ Remaining Static Electrical Characteristics are listed under "SCL4000B Series Family Specifications".

² T_{LOW} = -55°C for C, D, F, H device.

= -40°C for E device.

T_{HIGH} = +125°C for C, D, F, H device.

= +85°C for E device.

DYNAMIC CHARACTERISTICS (C_L = 50 pF, T_A = 25°C)

PARAMETER	V _{DD} (V _{Ddc})	Min.	Typ.	Max.	Units	
CLOCKED OPERATION						
PROPAGATION DELAY TIME Clock to Q ₁	t _{PLH} , t _{PML}	5	-	200	400	ns
		10	-	100	200	
		15	-	80	160	
Q ₁ to Q _{1,1}	t _{PLH} , t _{PML}	5	-	125	250	ns
		10	-	60	120	
		15	-	45	90	
OUTPUT TRANSITION TIME	t _{TLH} , t _{THL}	5	-	130	260	ns
		10	-	65	130	
		15	-	50	100	
MINIMUM CLOCK PULSE WIDTH	PW _{CL}	5	-	165	330	ns
		10	-	80	120	
		15	-	45	90	
MAXIMUM CLOCK FREQUENCY	f _{CL}	5	1.5	3.0	-	MHz
		10	4.0	8.0	-	
		15	5.5	11	-	
MAXIMUM CLOCK RISE AND FALL TIME	t _{r,CL} , t _{f,CL}	5	15	-	-	μs
		10	10	-	-	
		15	5	-	-	
RESET OPERATION						
PROPAGATION DELAY TIME	t _{PML}	5	-	350	700	ns
		10	-	175	350	
		15	-	130	260	
MINIMUM RESET PULSE WIDTH	PW _R	5	-	250	500	ns
		10	-	125	250	
		15	-	100	200	
RESET REMOVAL TIME	t _{rem}	5	-	250	500	ns
		10	-	75	150	
		15	-	60	120	

SCL4027B

CMOS DUAL J-K FLIP-FLOP

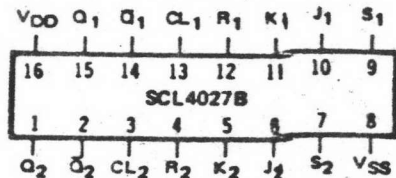
FEATURES

- ◆ Individual Set and Reset Controls
- ◆ Fully Static Operation
- ◆ Logic Edge-Clocked Design
- ◆ 8MHz Toggle Rate @ 10Vdc
- ◆ Balanced Output Drive Current Specifications

DESCRIPTION

The SCL4027B consists of two identical independent CMOS J-K master-slave Flip-Flops. The SCL4027B is useful in performing control, register, and toggle functions. Logic levels present at the J and K inputs along with internal self-steering control the state of each flip-flop; changes in the flip-flop state are synchronous with the positive-going transition of the Clock pulse. Set and Reset functions are independent of the Clock and are initiated when a high level signal is present at either the Set or Reset input.

CONNECTION DIAGRAM (all packages)



Add suffix for package:

- C 16-pin Cerdip F 16-pin Flat
- D 16-pin Ceramic H (Chip)
- E 16-pin Epoxy

RECOMMENDED OPERATING CONDITIONS

For maximum reliability:

DC Supply Voltage	VDD - VSS	3 to 15	Vdc
Operating Temperature	TA	65 to +125	°C
C, D, F, H Device		40 to +85	°C
E Device			

TRUTH TABLE

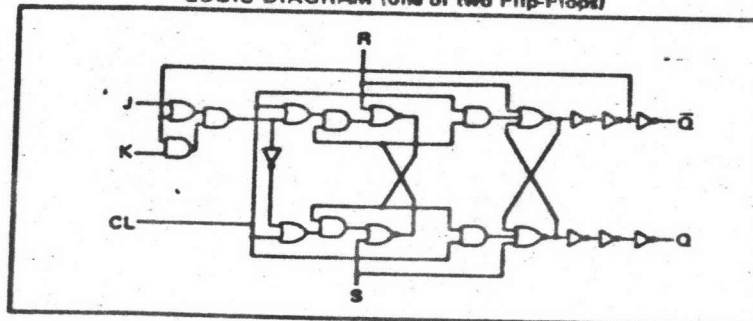
t _{n-1} INPUTS						t _n OUTPUTS		
CLA	J	K	S	R	Q	Q	Q	Q
1	X	0	0	0	0	1	0	
X	0	0	0	0	1	1	0	
0	X	0	0	0	0	0	1	
X	1	0	0	1	0	1		
X	X	0	0	X				(No Change)
X	X	X	1	0	X	1	0	
X	X	X	0	1	X	0	1	
X	X	X	1	1	X	1	1	

WHERE 1 = HIGH LEVEL
0 = LOW LEVEL

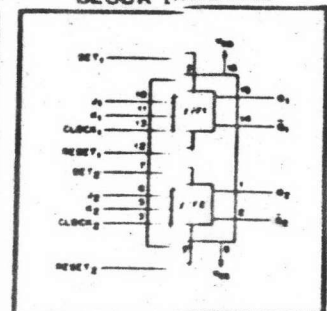
- A. LEVEL CHANGE
- X. DON'T CARE

- t_{n-1} REFERS TO THE INTERVAL PRIOR TO THE POSITIVE CLOCK PULSE TRANSITION
- t_n REFERS TO THE TIME INTERVAL AFTER THE POSITIVE CLOCK PULSE TRANSITION

LOGIC DIAGRAM (one of two Flip-Flops)



BLOCK DIAGRAM



ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

PARAMETER	V _{DD} (Vdc)	CONDITIONS	T _{LOW} ¹		+25°C			T _{HIGH} ²		Units
			Min.	Max.	Min.	Typ.	Max.	Min.	Max.	
QUIESCENT DEVICE CURRENT	I _{DD}	5	-	1.0	-	0.005	1.0	-	30	μA _{dc}
		10	-	2.0	-	0.01	2.0	-	60	
		15	-	4.0	-	0.02	4.0	-	120	

NOTES: ¹ Remaining Static Electrical Characteristics are listed under "SCL4000B Series Family Specifications".
² T_{LOW} = -55°C for C, D, F, H device.
 = -40°C for E device.

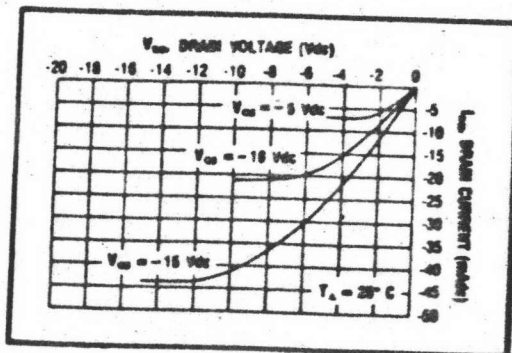
T_{HIGH} = +125°C for C, D, F, H device.
 = +85°C for E device.

³ This device has been designed for balanced output drive current specifications. Consult Family Specifications.

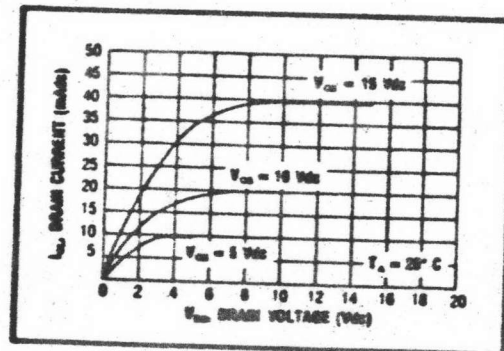
DYNAMIC CHARACTERISTICS (C_L = 50pF, T_A = 25°C)

PARAMETER	V _{DD} (Vdc)	Min.	Typ.	Max.	Units	
CLOCKED OPERATION						
PROPAGATION DELAY TIME	t _{PLH, tPHL}	5	-	175	350	ns
		10	-	80	160	
		15	-	60	120	
OUTPUT TRANSITION TIME	t _{FLM, tFHL}	5	-	100	200	ns
		10	-	50	100	
		15	-	40	80	
MINIMUM CLOCK PULSE WIDTH	PW _{CL}	5	-	165	330	ns
MAXIMUM CLOCK FREQUENCY	f _{CL}	5	1.5	3.0	-	MHz
		10	4.0	8.0	-	
		15	5.0	10	-	
MAXIMUM CLOCK RISE AND FALL TIME ¹	t _{CL, tCL}	5	15	-	-	μs
		10	5	-	-	
		15	3	-	-	
MINIMUM SETUP TIME	t _{setup}	5	-	100	200	ns
		10	-	50	100	
		15	-	40	80	
MINIMUM HOLD TIME	t _{hold}	5	-	-25	0	ns
		10	-	-10	0	
		15	-	-5	0	
SET AND RESET OPERATION						
PROPAGATION DELAY TIME S to Q, R to Q	t _{PLH}	5	-	150	300	ns
		10	-	70	140	
		15	-	55	110	
MINIMUM SET AND RESET PULSE WIDTH	PW _{S, PW_R}	5	-	100	200	ns
		10	-	50	100	
		15	-	40	80	
SET AND RESET REMOVAL TIME	t _{rem}	5	-	0	25	ns
		10	-	0	10	
		15	-	0	5	

¹ When units are cascaded, the maximum rise and fall times of the clock input should be equal to or less than the transition times of the data outputs driving data inputs, plus the propagation delay of the output driving stage for the output capacitive load.



Typical P-Channel
Source Current Characteristics



Typical N-Channel
Sink Current Characteristics

SCL4040AB

CMOS 12-STAGE BINARY COUNTER

FEATURES



- ◆ 12 Fully Static Stages
- ◆ All 12 Buffered Outputs Available
- ◆ Common Reset Line
- ◆ 8MHz Counting Rate @ 10Vdc
- ◆ All Inputs Buffered

DESCRIPTION

The SCL4040AB consists of 12-ripple-carry binary counter stages with appropriate input buffers and reset circuitry. The counter is reset to its "all 0's" state by a high level on the Reset input. The counter is advanced one count on the negative-going transition of each input pulse. Isolation from external noise and the effects of loads is provided by output buffering.

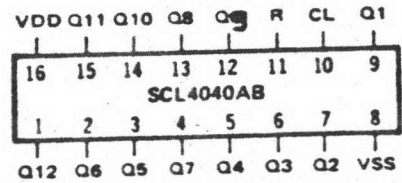
Applications include time delay circuits, counter controls, and frequency dividers.

TRUTH TABLE

Clock	Reset	Output State
	0	No Change
	0	Advance to next state
x	1	All Outputs are low

X = Don't Care

CONNECTION DIAGRAM (all packages)



Add suffix for package:

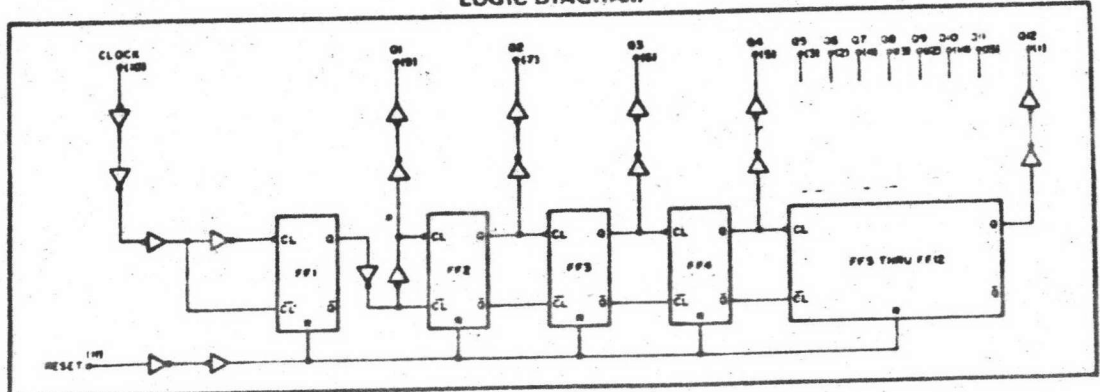
- C 16-pin Cerdip
- D 16-pin Ceramic
- E 16-pin Epoxy
- F 16-pin Flat
- H Chip

RECOMMENDED OPERATING CONDITIONS

For maximum reliability:

DC Supply Voltage	VDD - VSS	3 to 15	Vdc
Operating Temperature	TA	-55 to +125	°C
C, D, F, H Device		-40 to +85	°C
E Device			

LOGIC DIAGRAM



ELECTRICAL CHARACTERISTICS

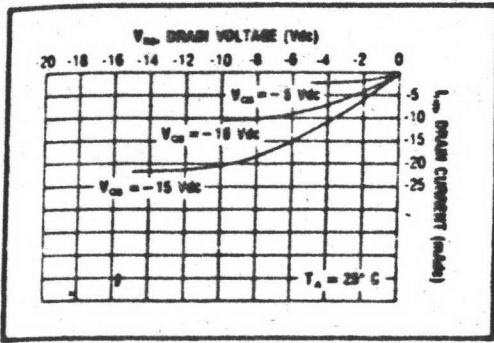
STATIC CHARACTERISTICS¹

PARAMETER	V _{DD} (Vdc)	CONDITIONS	T _{LOW} ²		+25°C			T _{HIGH} ²		Units			
			Min.	Max.	Min.	Typ.	Max.	Min.	Max.				
QUIESCENT DEVICE CURRENT	I _{DD}	V _{IN} =V _{SS} or V _{DD} All valid input combinations	5	5	-	0.05	5	-	150	μAdc			
			10	10	-	0.1	10	-	300				
			15	15	-	0.2	20	-	600				
OUTPUT HIGH (SOURCE) CURRENT C, D, F, H device	I _{OH}	V _{OH} =4.5V V _{OH} =9.5V V _{OH} =13.5V V _{IN} =V _{SS} or V _{DD}	5	-0.15	-	-0.12	-0.5	-	-0.08	-	mAdc		
			10	-0.37	-	-0.3	-1.15	-	-0.21	-			
			15	-1.25	-	-1.0	-4.5	-	-0.69	-			
			E device	5	-0.14	-	-0.12	-0.5	-	-0.10		-	mAdc
			10	-0.35	-	-0.3	-1.15	-	-0.25	-			
			15	-1.2	-	-1.0	-4.5	-	-0.65	-			
OUTPUT LOW (SINK) CURRENT C, D, F, H device	I _{OL}	V _{OL} =0.4V V _{OL} =0.5V V _{OL} =1.5V V _{IN} =V _{SS} or V _{DD}	5	0.15	-	0.12	0.5	-	0.08	-	mAdc		
			10	0.37	-	0.3	1.0	-	0.21	-			
			15	1.25	-	1.0	5.8	-	0.69	-			
			E device	5	0.14	-	0.12	0.5	-	0.10		-	mAdc
			10	0.35	-	0.3	1.0	-	0.25	-			
			15	1.2	-	1.0	5.8	-	0.65	-			

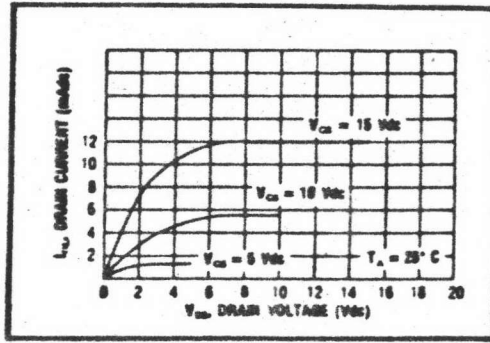
NOTES: ¹ Remaining Static Electrical Characteristics are listed under "SCL4000B Series Family Specifications".
² T_{LOW} = -55°C for C, D, F, H device.
 = -40°C for E device.
 T_{HIGH} = +125°C for C, D, F, H device.
 = +85°C for E device.

DYNAMIC CHARACTERISTICS (C_L = 50pF, T_A = 25°C)

PARAMETER	V _{DD} (Vdc)	Min.	Typ.	Max.	Units	
CLOCKED OPERATION						
PROPAGATION DELAY TIME Clock to Q1	t _{PLH, t_{PHL}}	5	-	200	400	ns
		10	-	100	200	
		15	-	80	160	
		Q ₁ to Q _{1, n}	t _{PLH, t_{PHL}}	5	-	
10	-	75	150			
15	-	60	120			
OUTPUT TRANSITION TIME	t _{TLH, t_{TNL}}	5	-	180	360	ns
10	-	90	180			
15	-	65	130			
MINIMUM CLOCK PULSE WIDTH	PW _{CL}	5	-	100	200	ns
10	-	50	100			
15	-	40	80			
MAXIMUM CLOCK FREQUENCY	f _{CL}	5	2.0	4.0	-	MHz
10	4.0	8.0	-			
15	5.0	10.0	-			
MAXIMUM CLOCK RISE AND FALL TIME	t _{CL, t_{CL}}	5	15	-	-	μs
10	15	-	-			
15	5	-	-			
RESET OPERATION						
PROPAGATION DELAY TIME	t _{PHL}	5	-	300	600	ns
10	-	150	300			
15	-	120	240			
MINIMUM RESET PULSE WIDTH	PW _R	5	-	150	300	ns
10	-	75	150			
15	-	60	120			
RESET REMOVAL TIME	t _{rem}	5	-	250	500	ns
10	-	125	250			
15	-	100	200			

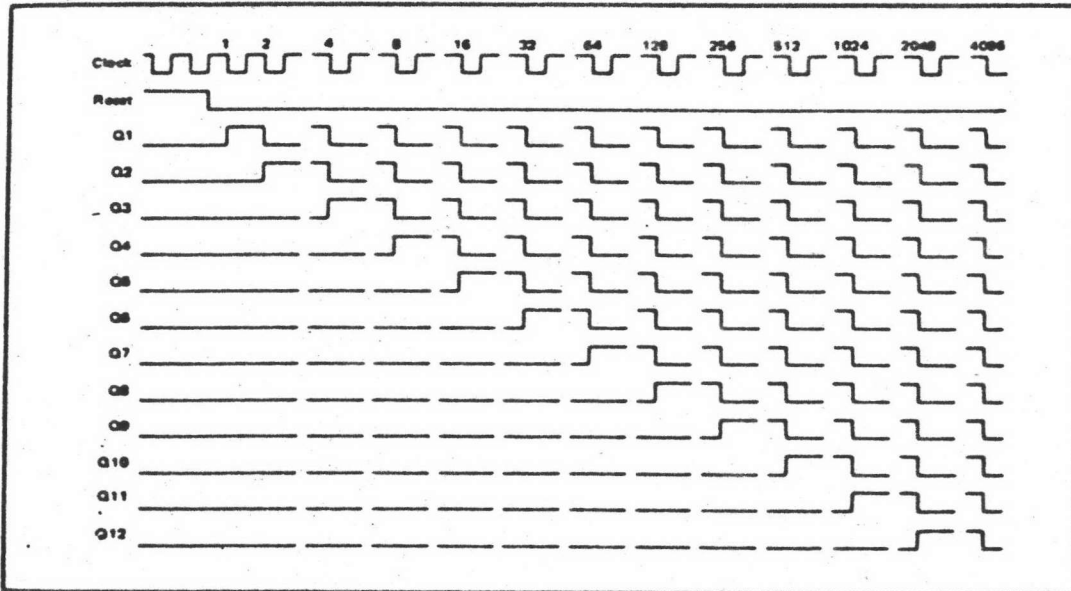


Typical P-Channel Source Current Characteristics

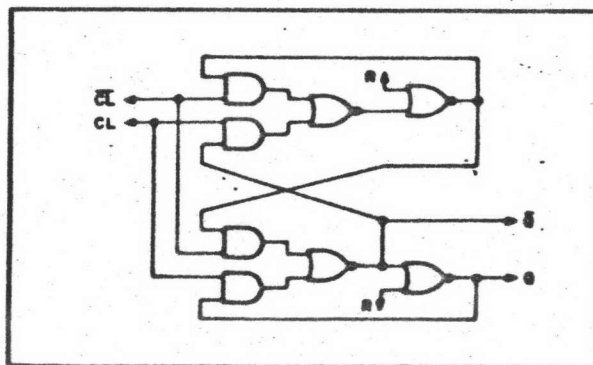


Typical N-Channel Sink Current Characteristics

TIMING DIAGRAM



TYPICAL COUNTER STAGE



SCL4069UB

FEATURES

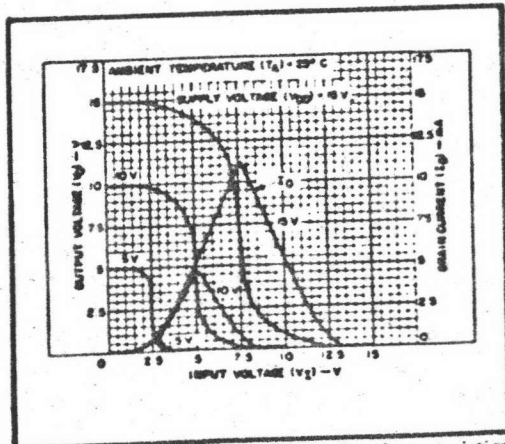
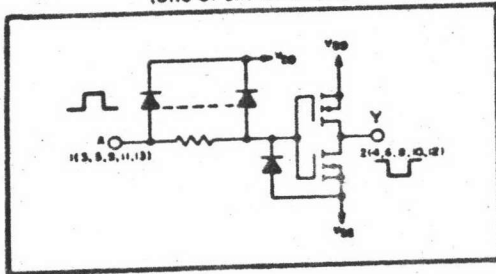
- ◆ Fully "B"-Series Compatible
- ◆ Diode Protection on all Inputs
- ◆ Balanced Output Drive Current Specifications
- ◆ Pin Compatible with 74C04

DESCRIPTION

The SCL4069UB consists of six CMOS inverter circuits. The device is intended for general-purpose inverter applications where the higher output drive and level-shifting feature of the SCL4009UB and SCL4049UB are not required.* The SCL4069UB is particularly useful for quasi-linear circuits such as oscillators (See Applications Information).

* For pin-to-pin compatibility with the SCL4009UB and SCL4049UB, the SCL4449UB is available.

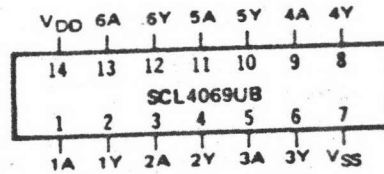
SCHEMATIC DIAGRAM (one of six inverters)



Typical current and voltage transfer characteristics

CMOS HEX INVERTER

CONNECTION DIAGRAM (all packages)



Add suffix for package:

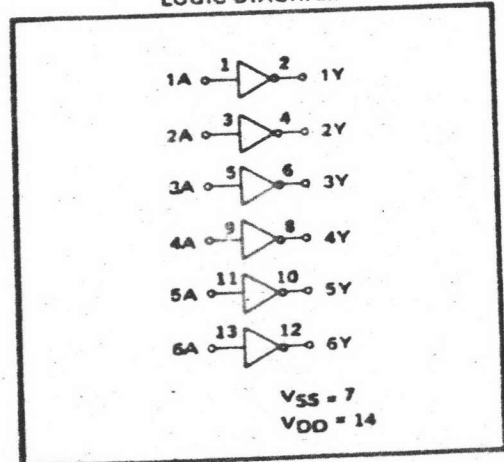
- C 14-pin Cerdip
- D 14-pin Ceramic
- E 14-pin Epoxy
- F 14-pin Flat
- H Chip

RECOMMENDED OPERATING CONDITIONS

For maximum reliability:

DC Supply Voltage	VDD - VSS	3 to 15	Vdc
Operating Temperature	TA	-55 to +125	°C
C, D, F, H Device		-40 to +85	°C
E Device			

LOGIC DIAGRAM



ELECTRICAL CHARACTERISTICS

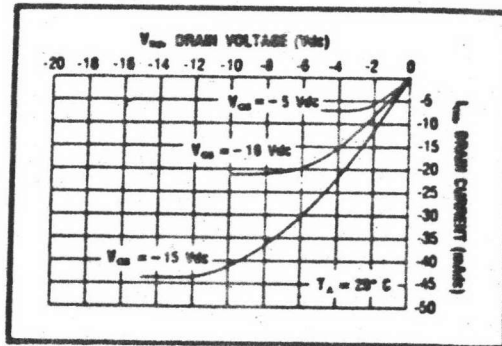
STATIC CHARACTERISTICS^{1,2}

PARAMETER	V _{DD} (Vdc)	CONDITIONS	T _{LOW} ³		+25°C			T _{HIGH} ³		Units
			Min.	Max.	Min.	Typ.	Max.	Min.	Max.	
QUIESCENT DEVICE CURRENT	V _{DD}	V _{IN} = V _{SS} or V _{DD} All valid input combinations	-	0.05	-	0.0005	0.05	-	1.5	μA _{dc}
			-	0.10	-	0.001	0.10	-	3.0	
			-	0.20	-	0.002	0.20	-	6.0	

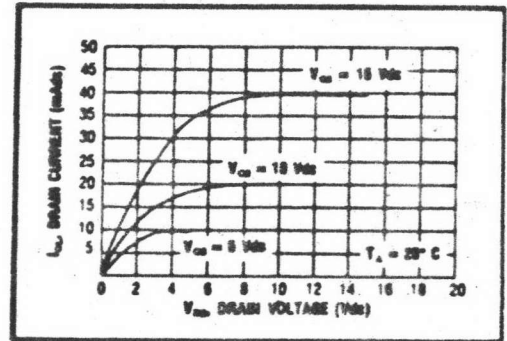
- NOTES: ¹ Remaining Static Electrical Characteristics are listed under "SCL4000B Series Family Specifications".
² T_{LOW} = -55°C for C, D, F, H device.
 = -40°C for E device.
 T_{HIGH} = +125°C for C, D, F, H device.
 = + 85°C for E device.
³ This device has been designed for balanced output drive current specifications. Consult Family Specifications.

DYNAMIC CHARACTERISTICS (C_L = 50pF, T_A = 25°C)

PARAMETER		V _{DD} (Vdc)	Min.	Typ.	Max.	Units
PROPAGATION DELAY TIME	t _{PLH} , t _{PHL}	5	-	60	120	ns
		10	-	30	60	
		15	-	25	50	
OUTPUT TRANSITION TIME	t _{TLN} , t _{THL}	5	-	100	200	ns
		10	-	50	100	
		15	-	40	80	

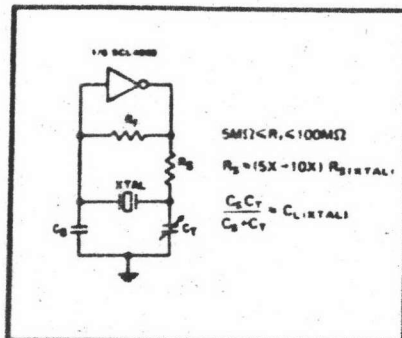


Typical P-Channel Source Current Characteristics

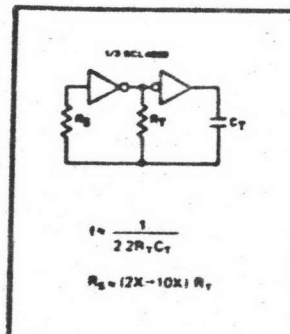


Typical N-Channel Sink Current Characteristics

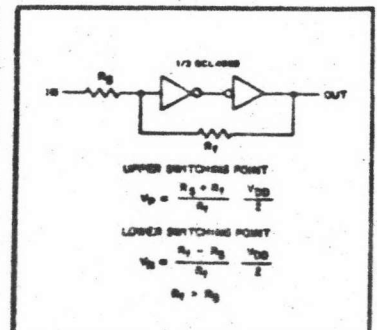
APPLICATIONS INFORMATION



Typical crystal oscillator circuit



Typical RC oscillator circuit



Input pulse shaping circuit (Schmitt Trigger)

SCL4511B

CMOS BCD-TO-SEVEN SEGMENT LATCH/DECODER/DRIVER

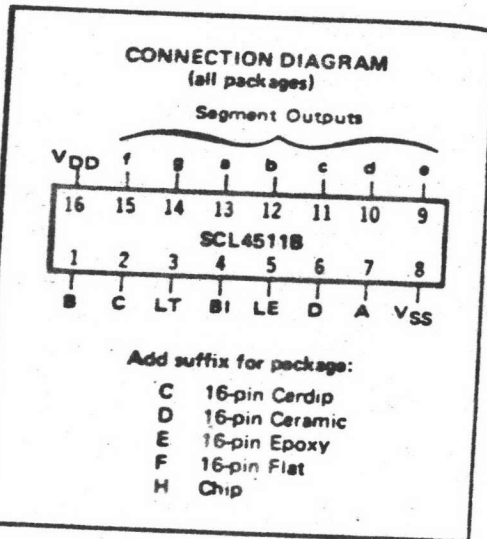
FEATURES

- ◆ High-Current Sourcing Bipolar Outputs (Up to 25 mA)
- ◆ Latched Storage of Input Code
- ◆ Blanking Input for Display Intensity Modulation
- ◆ Lamp Test Provision
- ◆ Readout Blanking for Illegal Input Combinations

DESCRIPTION

The SCL4511B provides the functions of a 4-bit storage latch, an 8421 BCD-to-seven segment decoder, and an output drive capability to source up to 25 mA of current. Lamp Test, Blanking, and Latch Enable inputs are used to test the display, turn off the display, and store a BCD code, respectively. It can be used with LED, incandescent, fluorescent, gas discharge, or liquid crystal readouts either directly or indirectly.

Applications include counter display drivers, seven-segment decimal display, and various clock, watch, and timer uses.

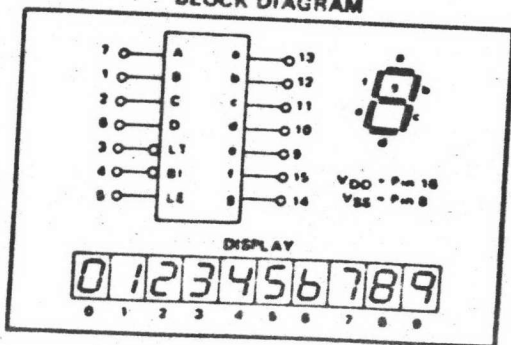


TRUTH TABLE

LE	BI	LT	D	C	B	A	a	b	c	d	e	f	g	DISPLAY
X	X	0	X	X	X	X	1	1	1	1	1	1	1	.8
X	0	1	X	X	X	X	0	0	0	0	0	0	0	Blank
0	1	1	0	0	0	0	1	1	1	1	1	0	0	0
0	1	1	0	0	0	1	0	1	1	0	0	0	0	1
0	1	1	0	0	1	0	1	1	0	1	0	1	0	2
0	1	1	0	1	0	1	1	1	1	0	0	1	0	3
0	1	1	0	1	0	0	0	1	1	0	0	1	1	4
0	1	1	0	1	1	0	1	0	1	1	0	1	1	5
0	1	1	0	1	1	0	0	0	1	1	1	1	1	6
0	1	1	0	1	1	1	1	1	0	0	0	0	0	7
0	1	1	1	0	0	0	1	1	1	1	1	1	1	8
0	1	1	1	0	0	1	1	1	1	1	1	1	1	Blank
0	1	1	1	0	1	0	0	0	0	0	0	0	0	Blank
0	1	1	1	0	1	1	0	0	0	0	0	0	0	Blank
0	1	1	1	1	0	0	0	0	0	0	0	0	0	Blank
0	1	1	1	1	1	0	0	0	0	0	0	0	0	Blank
1	1	1	X	X	X	X	0	0	0	0	0	0	0	Blank

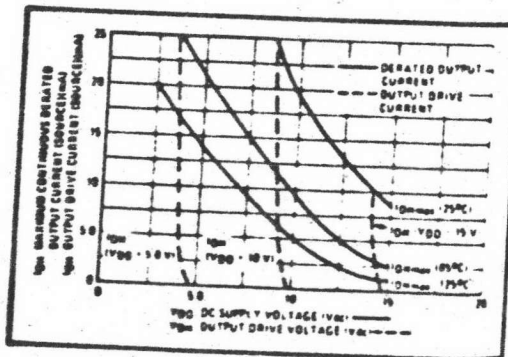
X = Don't care
 * Depends upon the BCD code applied during the 0 to 1 transition of LE.

BLOCK DIAGRAM



RECOMMENDED OPERATING CONDITIONS

For maximum reliability:
 DC Supply Voltage $V_{DD} - V_{SS}$ 3 to 15 V_{cc}
 Operating Temperature T_A
 C, D, F, H Device -55 to +125 °C
 E Device -40 to +85 °C



Typical P-Channel Source Current Characteristics

The maximum continuous (worst case) derated output drive current applies to a single output with all other outputs sourcing an equal amount of current. Operation above the derating curve at a given temperature is not recommended.

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS¹

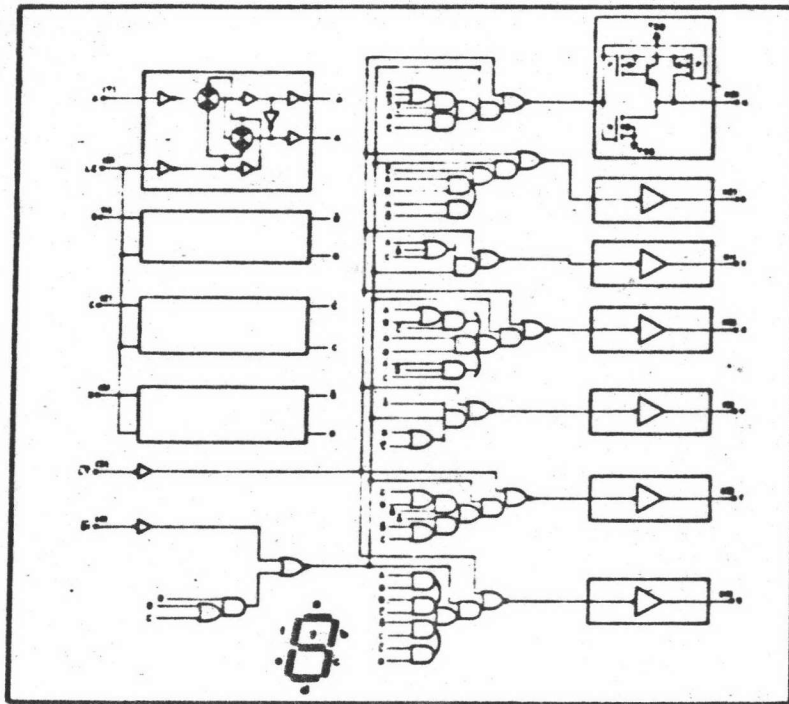
PARAMETER	V _{DD} (Vdc)	CONDITIONS	T _{AMB} ²		-25°C			Units		
			Min.	Max.	Min.	Typ.	Max.			
QUIESCENT DEVICE CURRENT ³	5	V _{IN} = V _{OH} or V _{OL} All valid input combinations	-	5	-	0.05	5	150	μA _{DC}	
	10		-	10	-	0.1	10	300		
	15		-	20	-	0.2	20	600		
OUTPUT DRIVE VOLTAGE	5	I _{OH} = 0 mA _{DC}	-	4.98	-	4.98	5.0	-	4.98	V _{dc}
			-5	-	-	-	4.25	-	-	
			-10	-	-	-	3.8	-	-	
			-15	-	-	-	3.95	-	-	
			-20	-	-	-	3.4	-	-	
	-25	-	-	-	3.5	-	-			
	10	I _{OH} = 0 mA _{DC}	-	9.98	-	9.98	10	-	9.95	V _{dc}
			-5	-	-	-	9.25	-	-	
			-10	-	-	-	9.0	-	-	
			-15	-	-	-	9.05	-	-	
			-20	-	-	-	8.8	-	-	
	-25	-	-	-	8.75	-	-			
	15	I _{OH} = 0 mA _{DC}	-	14.98	-	14.98	15	-	14.95	V _{dc}
			-5	-	-	-	14.25	-	-	
			-10	-	-	-	14.0	-	-	
-15			-	-	-	14.05	-	-		
-20			-	-	-	13.8	-	-		
-25	-	-	-	13.80	-	-				
OUTPUT LOW (SINK) CURRENT C, D, F, H devices	5	V _{OL} = 0.4V	1.9	-	1.5	3.4	-	1.1	mA _{DC}	
	10	V _{OL} = 0.5V	5.0	-	4.0	6.5	-	2.8		
	15	V _{OL} = 1.5V	13.8	-	11.0	24	-	7.7		
	E device	V _{IN} = V _{OH} or V _{OL}	V _{OL} = 0.4V	1.8	-	1.5	3.4	-		1.2
			V _{OL} = 0.5V	4.8	-	4.0	6.5	-		3.2
			V _{OL} = 1.5V	13.2	-	11.0	24	-		8.8

NOTES: ¹ Remaining Static Electrical Characteristics are listed under "SCL4000B Series Family Specifications".
² T_{Low} = 55°C for C, D, F, H devices.
 = 40°C for E device.
³ T_{High} = -125°C for C, D, F, H devices.
 = 85°C for E device.

DYNAMIC CHARACTERISTICS (C_L = 50pF, T_A = 25°C)

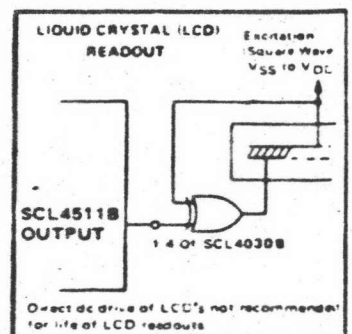
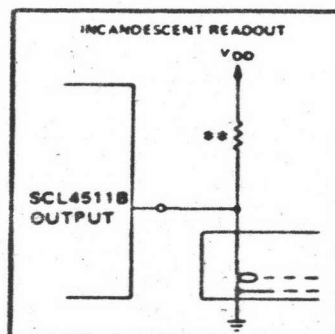
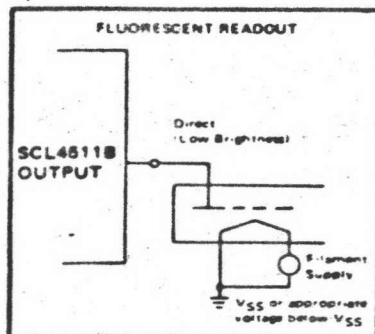
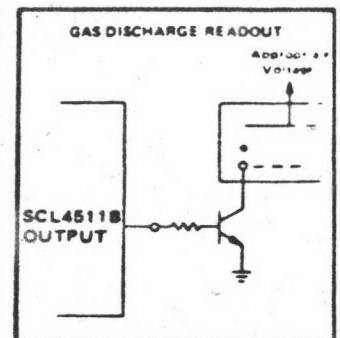
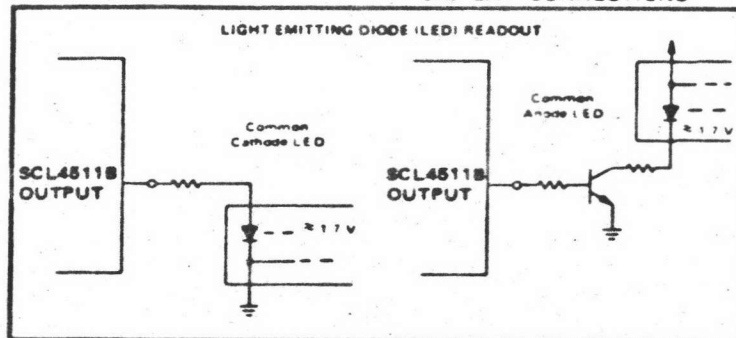
PARAMETER	V _{DD} (Vdc)	Min.	Typ.	Max.	Units	
PROPAGATION DELAY TIME From Data Inputs	t _{PLH}	5	-	850	1300	ns
		10	-	250	500	
		15	-	200	400	
	t _{PHL}	5	-	750	1500	ns
		10	-	300	600	
		15	-	200	400	
From Blanking Input	t _{PLH}	5	-	300	600	ns
		10	-	125	250	
		15	-	100	200	
	t _{PHL}	5	-	500	1000	ns
		10	-	200	400	
		15	-	180	320	
From Latch Test Input	t _{PLH}	5	-	300	600	ns
		10	-	120	240	
		15	-	90	180	
	t _{PHL}	5	-	325	650	ns
		10	-	130	260	
		15	-	95	190	
OUTPUT TRANSITION TIME	t _{PLZ}	5	-	90	180	ns
		10	-	48	96	
		15	-	35	70	
	t _{PHZ}	5	-	1000	2000	ns
		10	-	1000	2000	
		15	-	1000	2000	
MINIMUM DATA INPUT SETUP TIME	t _{setup}	5	-	90	180	ns
	10	-	48	96		
	15	-	35	70		
MINIMUM DATA INPUT HOLD TIME	t _{hold}	5	-	90	9	ns
	10	-	48	9		
	15	-	35	0		
MINIMUM LATCH ENABLE PULSE WIDTH	PW _{LE}	5	-	280	520	ns
	10	-	110	220		
	15	-	85	130		

LOGIC DIAGRAM



APPLICATIONS INFORMATION

DISPLAY CONNECTIONS



**A filament pre-warm resistor is recommended to reduce filament thermal shock and increase the effective cold resistance of the filament.



MOS RAMs

MM2102, MM2102-1, MM2102-2 1024-bit fully decoded static random access memories

general description

The MM2102 family of 1024 word by one bit static random access read write memories are manufactured using N-channel enhancement mode silicon gate technology. Static storage cells eliminate the need for clocks and refresh. Data in and data out have the same polarity and the read operation is nondestructive.

Low threshold silicon gate N-channel technology allows complete DTL/TTL compatibility of all inputs and outputs as well as a single +5V supply. The separate chip enable input (CE) controlling the TRI-STATE[®] output allows easy memory expansion by OR-tying individual devices to a data bus.

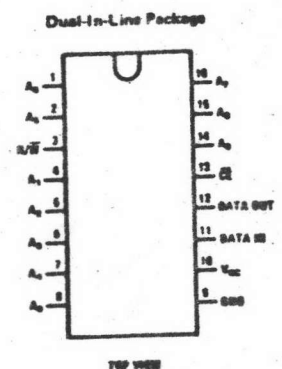
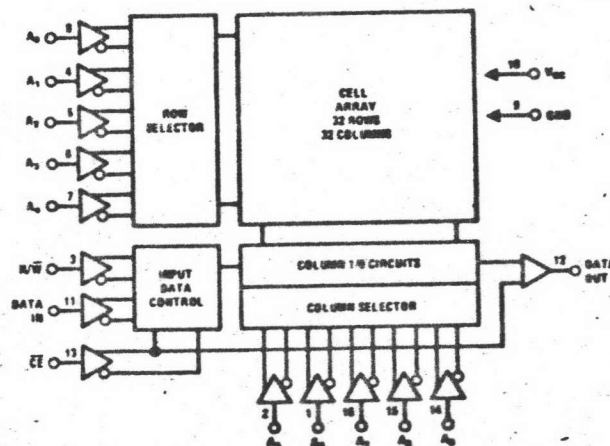
The simple interface and high performance make the MM2102 family ideally suited for those applications, for large and small storage capacity, where cost is an important design consideration.

features

- Single +5V supply
- All inputs and output directly DTL/TTL compatible
- Static operation—no clocks or refreshing required
- Low power 150 mW typ
- Fast access

MM2102	1 μ s
MM2102-1	500 ns
MM2102-2	650 ns
- TRI-STATE output for bus interface
- Chip enable allows simple memory expansion
- On chip address decode
- All inputs protected against static discharge
- Low cost 16-pin Epoxy B package

block and connection diagrams



Order Number MM2102D,
MM2102-1D or MM2102-2D
See Package 3

Order Number MM2102N,
MM2102-1N or MM2102-2N
See Package 15

absolute maximum ratings (Note 1)

Voltage at Any Pin	-0.5V to +7.0V
Operating Temperature Range	0°C to +70°C
Storage Temperature Range	-65°C to +150°C
Power Dissipation	1W
Lead Temperature (Soldering, 10 seconds)	300°C

dc electrical characteristics(T_A within operating temperature range, V_{CC} = 5V ±5%, unless otherwise noted.)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
Logical "1" Input Voltage (V _{IH})		2.2		V _{CC}	V
Logical "0" Input Voltage (V _{IL})		-0.5		0.65	V
Logical "1" Output Voltage (V _{OH})	I _{OH} = -100μA	2.2			V
Logical "0" Output Voltage (V _{OL})	I _{OL} = 1.9 mA			0.45	V
Input Load Current (I _{LI})	V _{IN} = 0 to 5.25V			10	μA
Output Leakage Current (I _{LOH})	\overline{CE} = 2.2V, V _{OUT} = 4.0V			10	μA
Output Leakage Current (I _{LOL})	\overline{CE} = 2.2V, V _{OUT} = 0.45V			-100	μA
Power Supply Current (I _{CC1})	All Inputs = 5.25V, Data Out Open, T _A = 25°C		30	60	mA
Power Supply Current (I _{CC2})	All Inputs = 5.25V, Data Out Open, T _A = 0°C			70	mA

ac electrical characteristics(T_A within operating temperature range, V_{CC} = 5V ±5%, unless otherwise specified.)

See ac test circuit and switching time waveforms.

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
READ CYCLE					
Read Cycle (t _{RC})					
MM2102	R/ \overline{W} = V _{IH}	1000			ns
MM2102-1	R/ \overline{W} = V _{IH}	500			ns
MM2102-2	R/ \overline{W} = V _{IH}	850			ns
Access Time (t _A)					
MM2102				1000	ns
MM2102-1				500	ns
MM2102-2				650	ns
Chip Enable to Output Time (t _{CO})					
MM2102				500	ns
MM2102-1				350	ns
MM2102-2				400	ns
Previous Read Data Valid with Respect to Address (t _{OH1})		50			ns
Previous Read Data Valid with Respect to Chip, Enable (t _{OH2})		0			ns

ac electrical characteristics (con't)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
WRITE CYCLE					
Write Cycle (t_{WC})					
MM2102		1000			ns
MM2102-1		500			ns
MM2102-2		650			ns
Address to Write Set-up Time (t_{AW})					
MM2102		200			ns
MM2102-1		150			ns
MM2102-2		200			ns
Write Pulse Width (t_{WP})					
MM2102		750			ns
MM2102-1		300			ns
MM2102-2		400			ns
Write Recovery Time (t_{WR})		50			ns
Data Set-up Time (t_{DW})					
MM2102		800			ns
MM2102-1		330			ns
MM2102-2		450			ns
Data Hold Time (t_{DH})		100			ns
Chip Enable to Write Set-up Time (t_{CW})					
MM2102		900			ns
MM2102-1		400			ns
MM2102-2		550			ns
CAPACITANCE					
Input Capacitance (All Inputs) (C_{IN}) (Note 4)	$V_{IN} = 0V, T_A = 25^\circ C, f = 1.0 \text{ MHz}$ (Note 2)		3.0	5.0	pF
Output Capacitance (C_{OUT}) (Note 4)	$V_{OUT} = 0V, T_A = 25^\circ C, f = 1.0 \text{ MHz}$ (Note 2)		7.0	10.0	pF

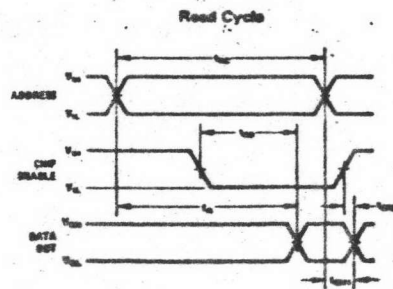
Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Capacitance is guaranteed by periodic testing.

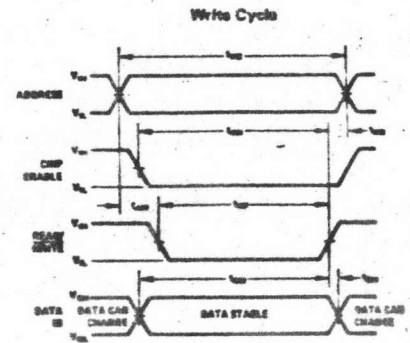
Note 3: Positive true logic notation is used: Logical "1" = most positive voltage level, Logical "0" = most negative voltage level.

Note 4: Typical values are for $T_A = 25^\circ C$ and nominal supply voltage.

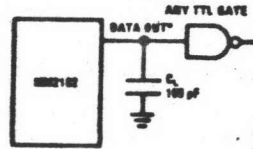
switching time waveforms



Notes: All times measured with respect to 1.5V level with 1 and 1.5 pF.

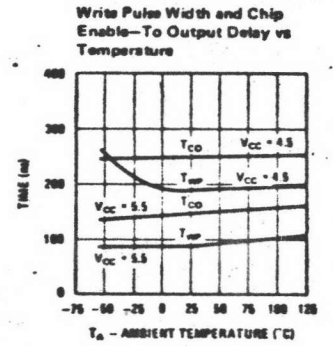
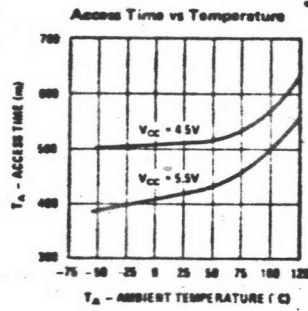
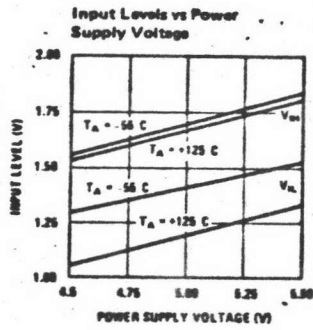
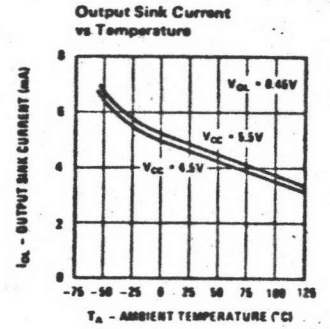
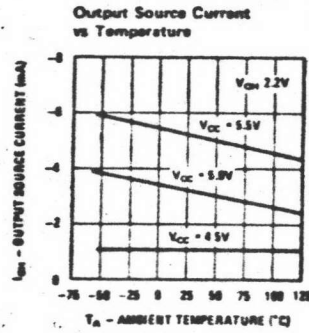
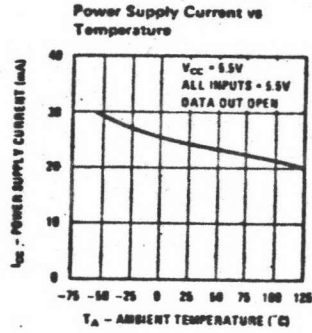


ac test circuit



*Delay times measured at 682102 output.

typical performance characteristics



DECADE COUNTER

54/74

SPEED/PACKAGE AVAILABILITY

54 F.W 74 A.F
54LS F.W 74LS A.F

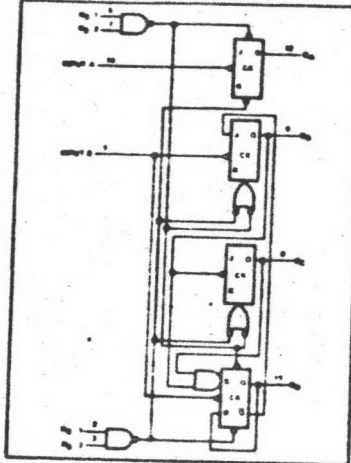
DESCRIPTION

This monolithic counter contains four master-slave flip-flops and additional gating to provide a divide-by-two counter and a three-stage binary counter for which the count cycle length is divide-by-five.

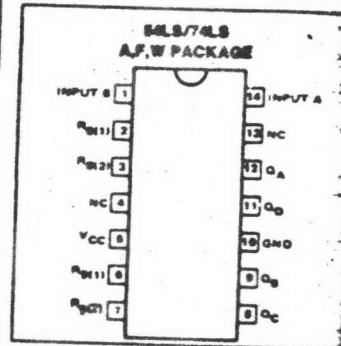
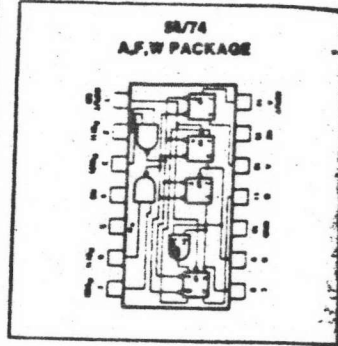
The 54/74LS90 also has a gated zero reset and gated set-to-nine inputs for use in BCD nine's complement applications.

To use its maximum count length of this counter, the B input is connected to the Q_A output. The input count pulses are applied to input A and the outputs are as described in the function table. A symmetrical divide-by-ten count can be obtained by connecting the Q_D output to the A input and applying the input count to the B input which gives a divide-by-ten square wave at output Q_A .

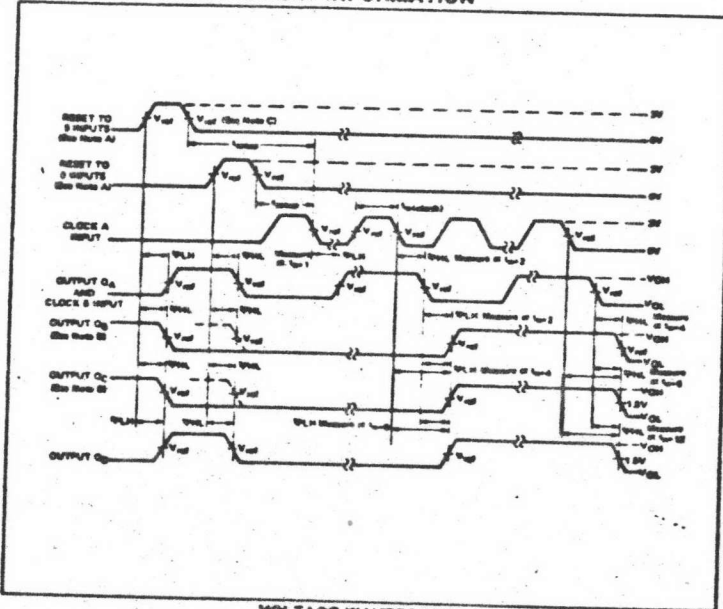
BLOCK DIAGRAM 54LS/74LS



PIN CONFIGURATION



PARAMETER MEASUREMENT INFORMATION



VOLTAGE WAVEFORMS

- A. Each reset input is tested separately with the other reset at 4.5 V
 - B. Reference waveforms are shown with dashed lines
 - C. $V_{IL} = 1.5 V$
- Load circuit is shown at front of section for output pole outputs

DECADE COUNTER

54/7490

SWITCHING CHARACTERISTICS $V_{CC} = 5V, T_A = 25^\circ C$

TEST CONDITIONS			54/74			54/74LS			UNIT
			$C_L = 15pF, R_L = 400\Omega$			$C_L = 15pF, R_L = 2k\Omega$			
PARAMETER	FROM INPUT	TO OUTPUT	MIN	TYP	MAX	MIN	TYP	MAX	
f_{Count} Count frequency	A	Q_A	10	18		32	42		MHz
	B	Q_B				16			
$t_{r(Clock)}$ Width of clock pulse	A	Q	50			15			ns
	B	Q				30			
	Reset	Q				15			
$t_{r(Reset)}$ Width of reset pulse			50			25			ns
Propagation delay times									ns
t_{PLH} Low-to-high	Input Count Pulse	Q_C		80	100				
t_{PLH} High-to-low				80	100				
t_{PLH} Low-to-high	A	Q_A				10	18		
			t_{PLH} High-to-low				12	18	
t_{PLH} Low-to-high	A	Q_D				32	48		
			t_{PLH} High-to-low				34	50	
t_{PLH} Low-to-high	B	Q_B				10	16		
			t_{PLH} High-to-low				14	21	
t_{PLH} Low-to-high	B	Q_C				21	32		
			t_{PLH} High-to-low				23	35	
t_{PLH} Low-to-high	B	Q_D				21	32		
			t_{PLH} High-to-low				23	35	
t_{PLH} High-to-low	Set-to-0	Any				26	40		
t_{PLH} Low-to-high	Set-to-0	Q_A, Q_D				20	30		
t_{PLH} High-to-low	Set-to-0	Q_B, Q_C				26	40		

See input and typical waveforms shown at front of section

BCD COUNT SEQUENCE
(See Note A)

COUNT	OUTPUT			
	Q_D	Q_C	Q_B	Q_A
0	L	L	L	L
1	L	L	L	H
2	L	L	H	L
3	L	L	H	H
4	L	H	L	L
5	L	H	L	H
6	L	H	H	L
7	L	H	H	H
8	H	L	L	L
9	H	L	L	H

BI-QUINARY (5-2)
(See Note B)

COUNT	OUTPUT			
	Q_A	Q_D	Q_C	Q_B
0	L	L	L	L
1	L	L	L	H
2	L	L	H	L
3	L	L	H	H
4	L	H	L	L
5	H	L	L	L
6	H	L	L	H
7	H	L	H	L
8	H	L	H	H
9	H	H	L	L

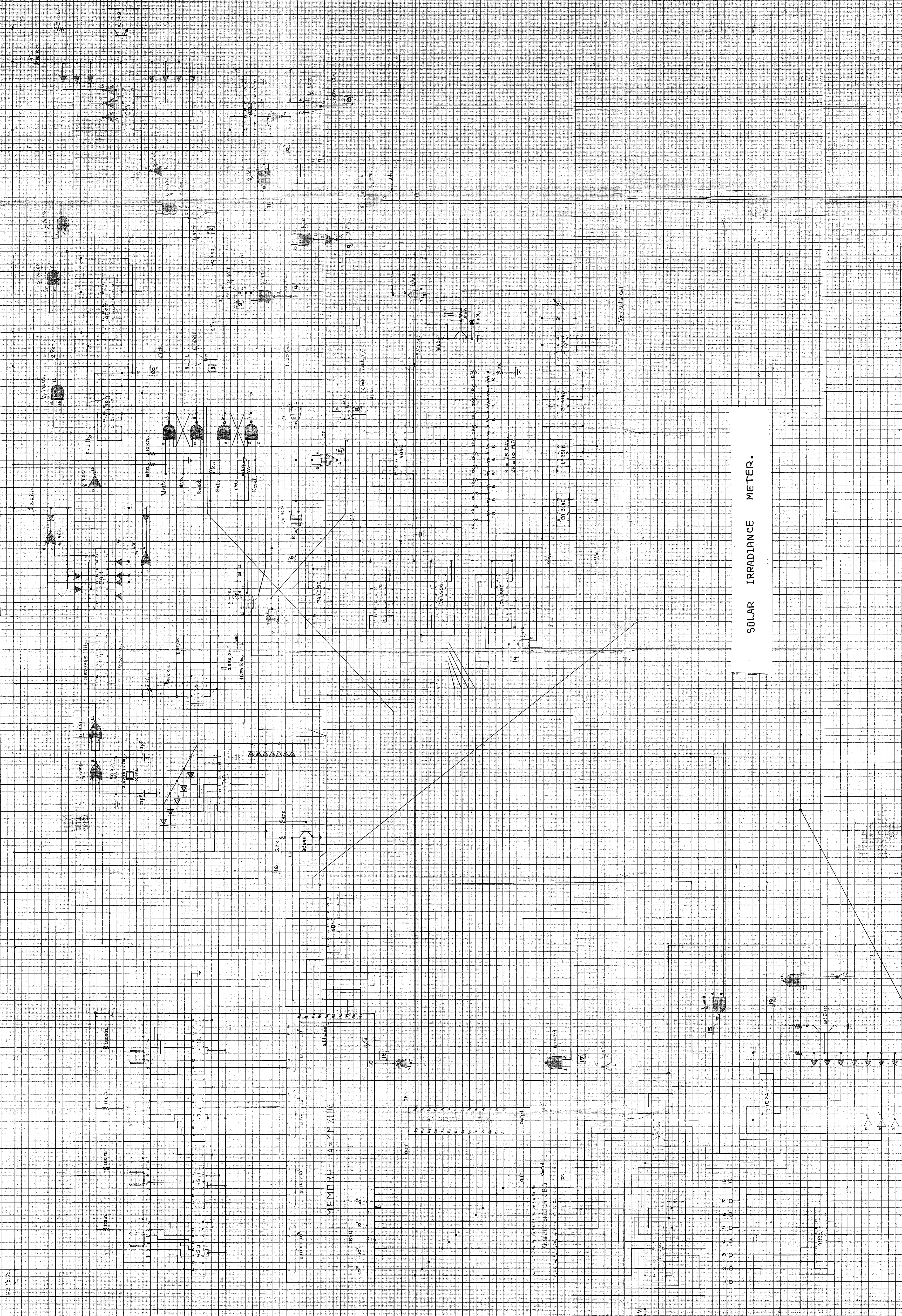
RESET/COUNT FUNCTION TABLE

RESET INPUTS				OUTPUT			
$R_{A(1)}$	$R_{A(2)}$	$R_{B(1)}$	$R_{B(2)}$	Q_B	Q_C	Q_B	Q_A
H	H	L	X	L	L	L	L
H	H	X	L	L	L	L	L
X	X	H	H	H	L	L	H
X	L	X	L				COUNT
L	X	X	X				COUNT
L	X	X	L				COUNT
X	L	L	X				COUNT

- NOTES:
 A. Output Q_A is connected to input B for BCD count.
 B. Output Q_D is connected to input A for bi-quinary count.
 C. Output Q_A is connected to input B.
 D. H - high level, L - low level, X - irrelevant

ภาคผนวก ค.

แผนภาพแสดงวงจรของเครื่องวัดการรับรังสีของดวงอาทิตย์



SOLAR IRRADIANCE METER.

MEMORY 45MM 210Z

MEMORY 45MM 210Z

MEMORY 45MM 210Z

MEMORY 45MM 210Z

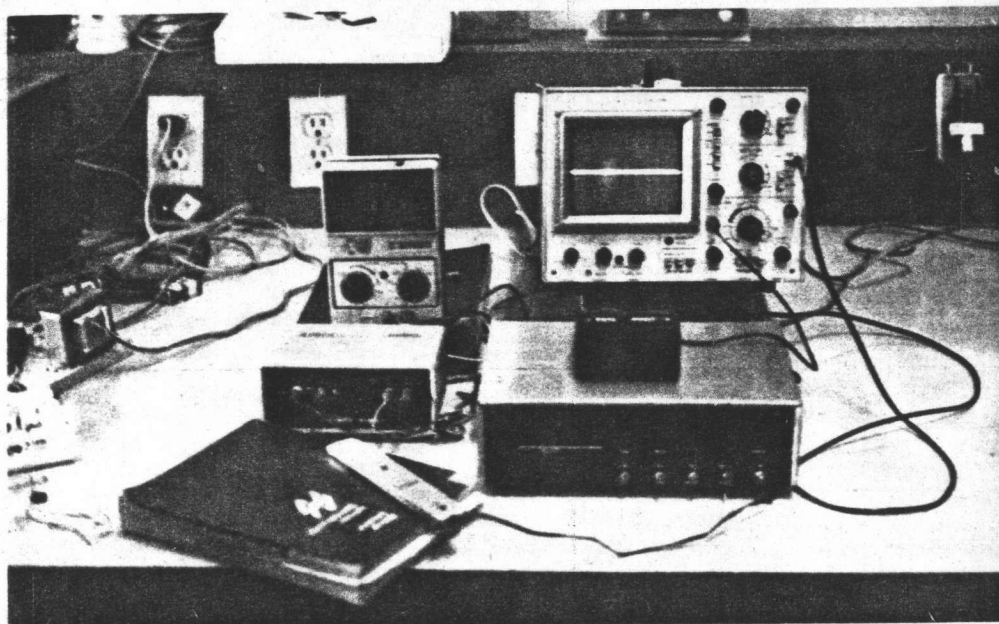
MEMORY 45MM 210Z

MEMORY 45MM 210Z

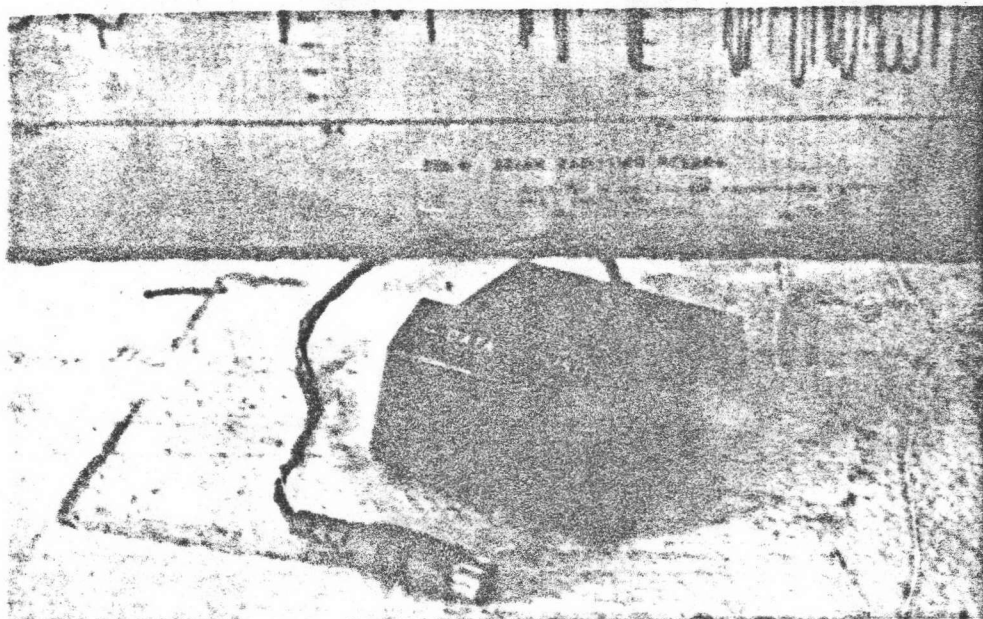
MEMORY 45MM 210Z

ภาคผนวก ง.

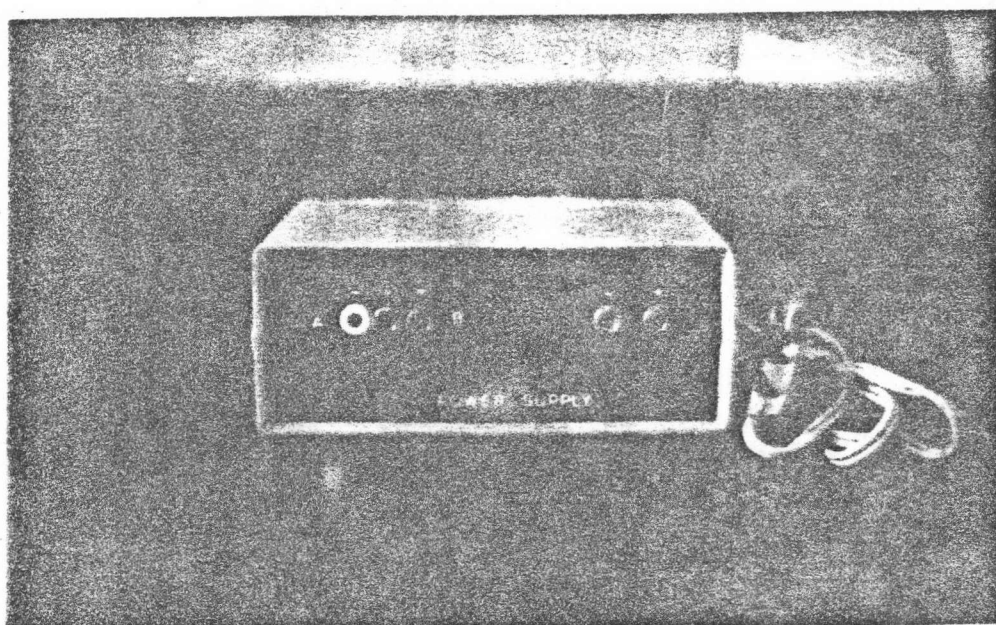
รูปภาพแสดงลักษณะของเครื่องวัดการรับรังสีของดวงอาทิตย์



รูปที่ 1. เครื่องวัดการรับรังสีของดวงอาทิตย์ เครื่องบอกตำแหน่งและแหล่งจ่ายไฟ



รูปที่ 2 เครื่องควบคุม 2



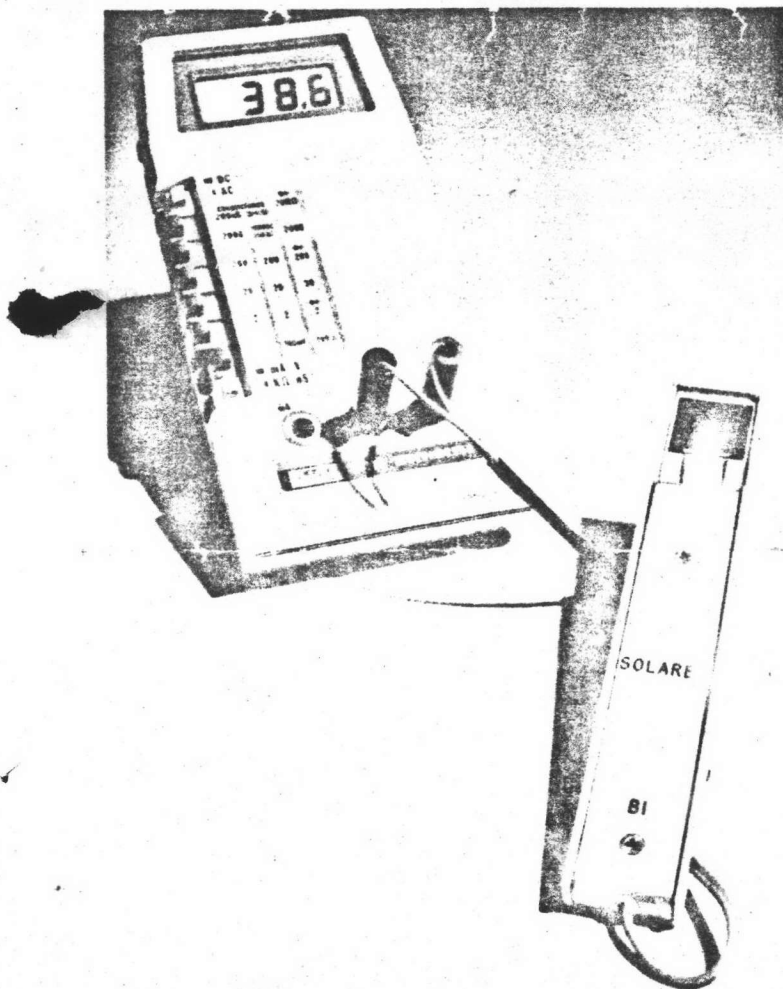
รูปที่ 3 เครื่องจ่ายไฟ

ภาคผนวก จ.

ลักษณะของเซลล์แสงอาทิตย์อ้างอิงที่ใช้สำหรับเครื่องวัดการรับรังสีของดวงอาทิตย์



THE REFERENCE SOLAR CELL



Meter not included

The Solarex Reference Cell comprises a premium-quality silicon solar cell and a precision resistor heat-sinked and encapsulated in a rugged, compact (1-1/2" X 6" X 1/4") anodized aluminum case. Used in conjunction with an accurate millivoltmeter, the Reference Cell enables precise solar measurements including:

- sunlight intensity measurements;
- design measurements for photovoltaic and solar thermal systems;
- determination of photovoltaic cell and module efficiency;
- calibration of sun simulators and measuring instruments.

The Reference Cell utilizes a broad-response Solarex silicon cell of International Space Standard size (2 cm X 2 cm) and quality, encapsulated in specially formulated UV-stable clear silicone rubber. The cell's high-technology features include:

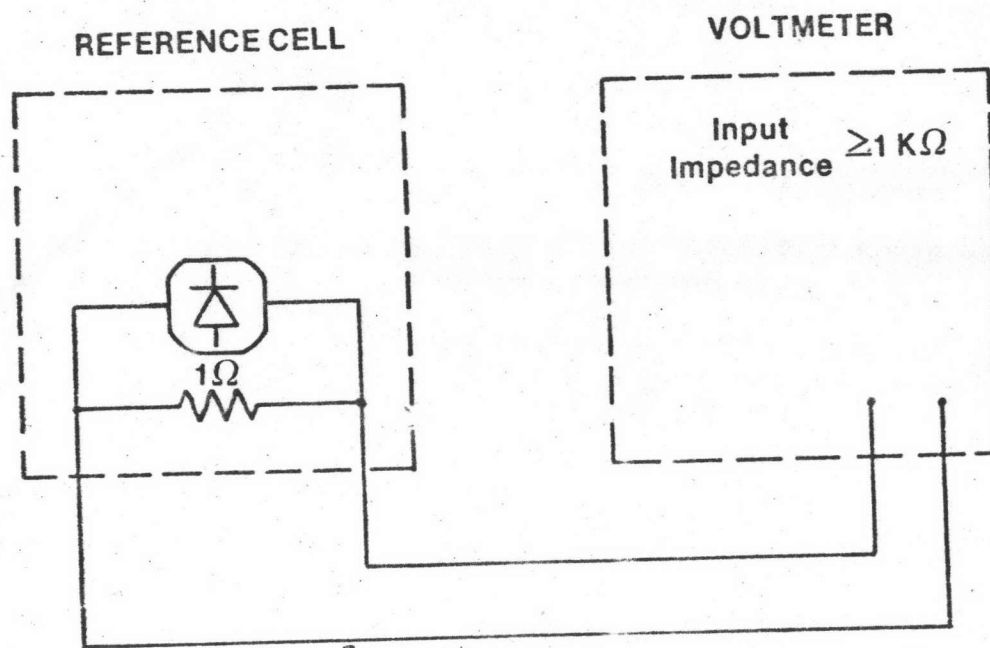
- photolithographically applied Trimet™ current-collecting metallization;¹
- precision quarter-wavelength tantalum oxide antireflective coating;
- P⁺ back surface field for wide spectral response.

Reference Cells are individually calibrated for Air Mass One (AM1) full-sun intensity (1 kW/m²) at 25°C. The output voltage produced across the integral 1-ohm shunt resistor under these conditions is stamped on the unit's nameplate. This low shunt resistance maintains the cell voltage near short-circuit conditions (where current precisely tracks illumination) and provides very low output impedance, assuring precise measurement regardless of voltmeter impedance. Consequently, the Reference Cell's output voltage provides a precise measure of sunlight intensity.

¹"Trimet" is Solarex's trademark for its non-corroding titanium/palladium/silver cell metallization.

As an example of Reference Cell use, assume the object is to determine a site's insolation with reference to AM1 standards. Also assume the Cell in use produces 148 mV under calibration conditions. At the appointed measurement time, the Cell produces 94 mV; sunlight intensity at that time, therefore, is:

$$\frac{94\text{mV}}{148\text{mV}} = 0.635 \text{ suns or } 635 \text{ W/m}^2$$



SCHEMATIC

CALIBRATION

Reference Cells are calibrated against a Solarex Standard Cell, which is standardized using an Eppley pyranometer (Model 8-48). Calibration reference for this pyranometer is the Eppley primary standard group of Angstrom Pyrheliometers, which are in close agreement (better than 0.5%) with the primary standards maintained at the National Physical Laboratory in London and the National Research Council in Ottawa. In addition, Solarex Standard Cells are checked against balloon-flown cells of similar spectral response, providing calibration verification for the broader extraterrestrial radiation spectrum.

All Reference Cell components are of the highest quality, and will not degrade or change value for many years. Readings may be affected, however, by marring or contamination (fingerprints, etc.) of the encapsulant surface. This surface should be cleaned periodically with alcohol or soap and a damp cloth.

Solarex recommends periodic recalibration for heavily used units and applications requiring extreme precision over extended time periods. Both recalibration and resurfacing service (for units displaying encapsulant abrasion) are available from Solarex.

ประวัติเขียน

นายไพสิฐ คันทะพงษ์ เกิดเมื่อวันที่ 30 มกราคม พ.ศ. 2522 ที่กรุงเทพฯ
 สำเร็จการศึกษาปริญญาวิศวกรรมศาสตรบัณฑิต สาขาวิศวกรรมไฟฟ้าสื่อสารและไฟฟ้ากำลัง
 จากมหาวิทยาลัยขอนแก่น เมื่อปี พ.ศ. 2522

